

FIG. 2A

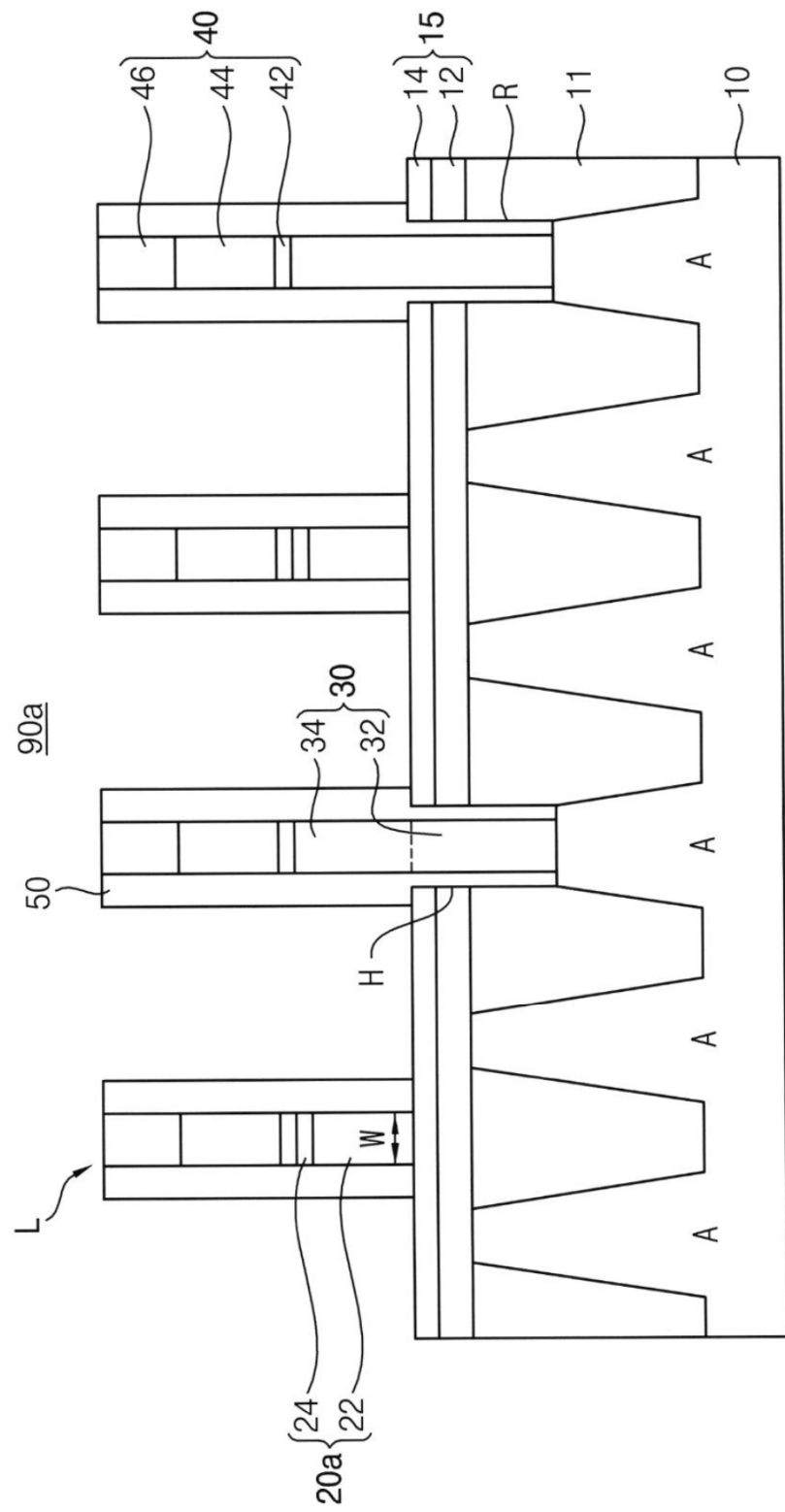
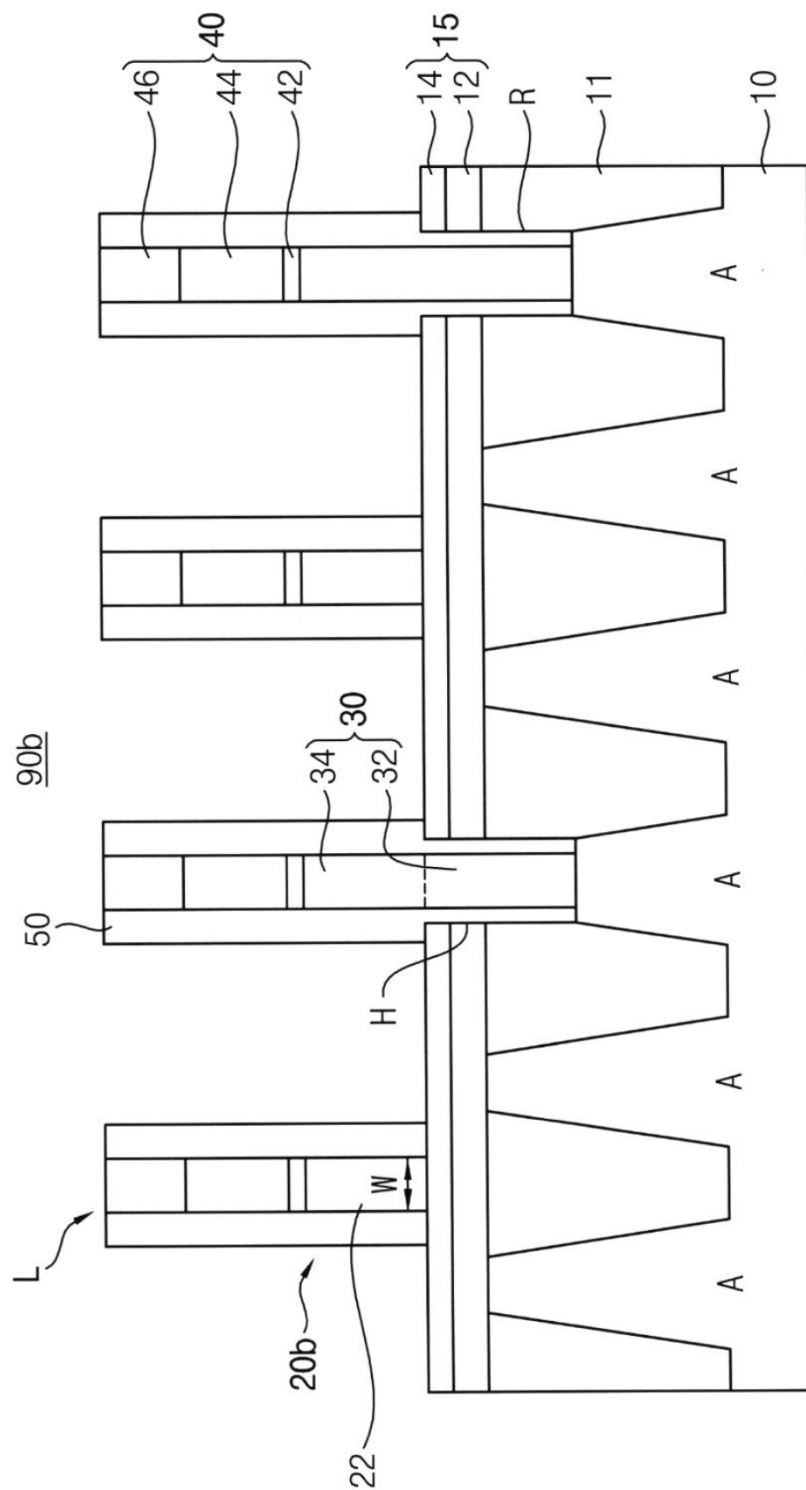


FIG. 2B



1000



FIG. 4A

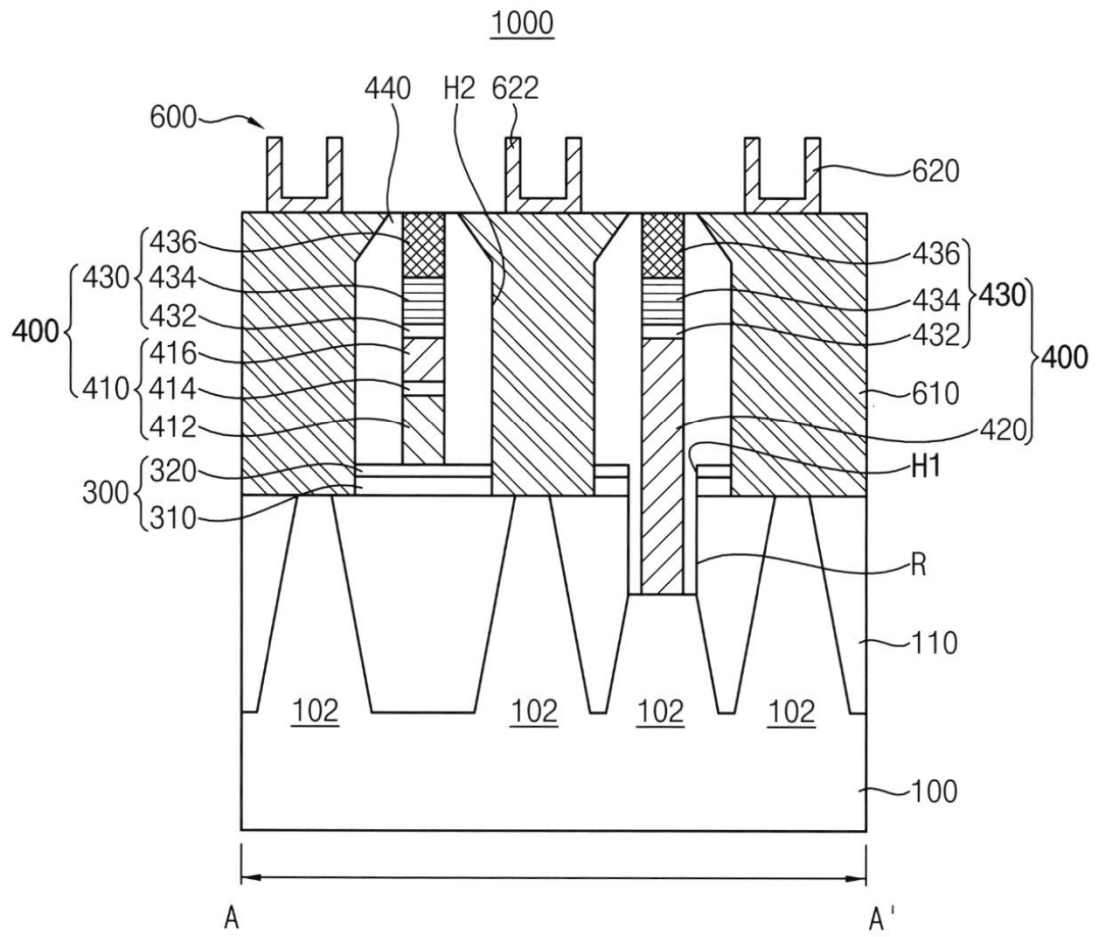


FIG. 4B

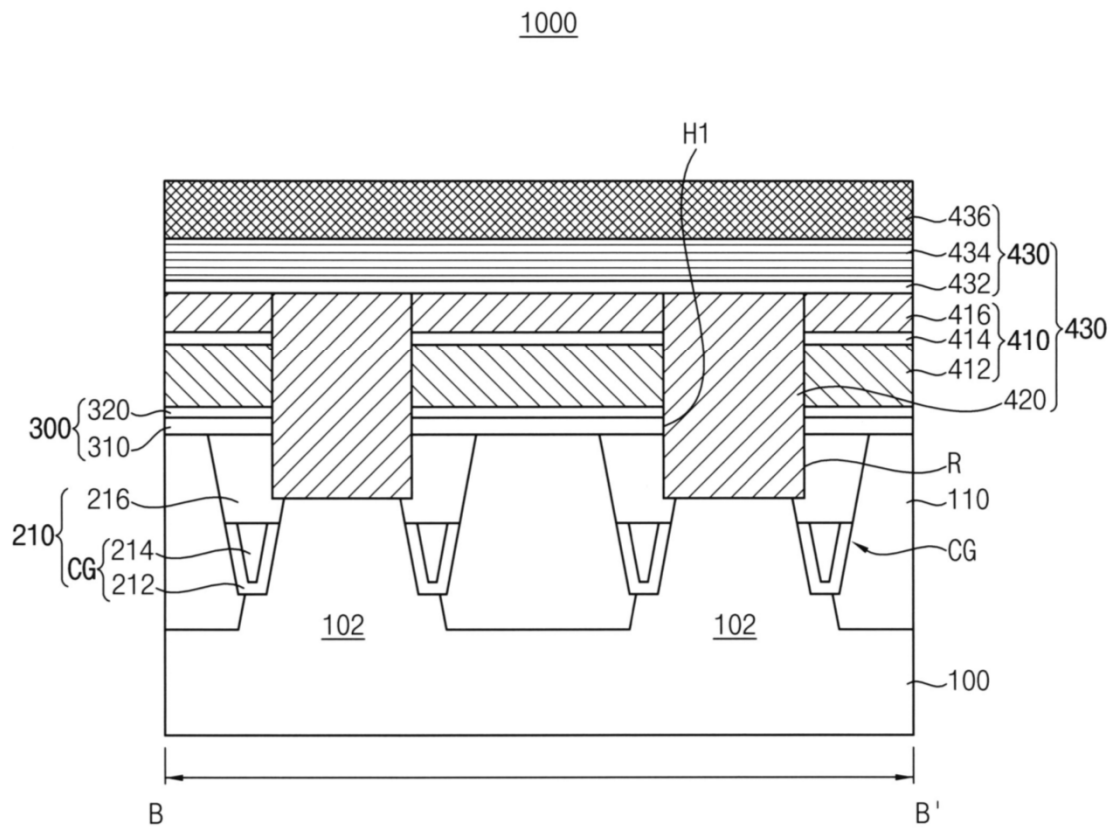


FIG. 4C

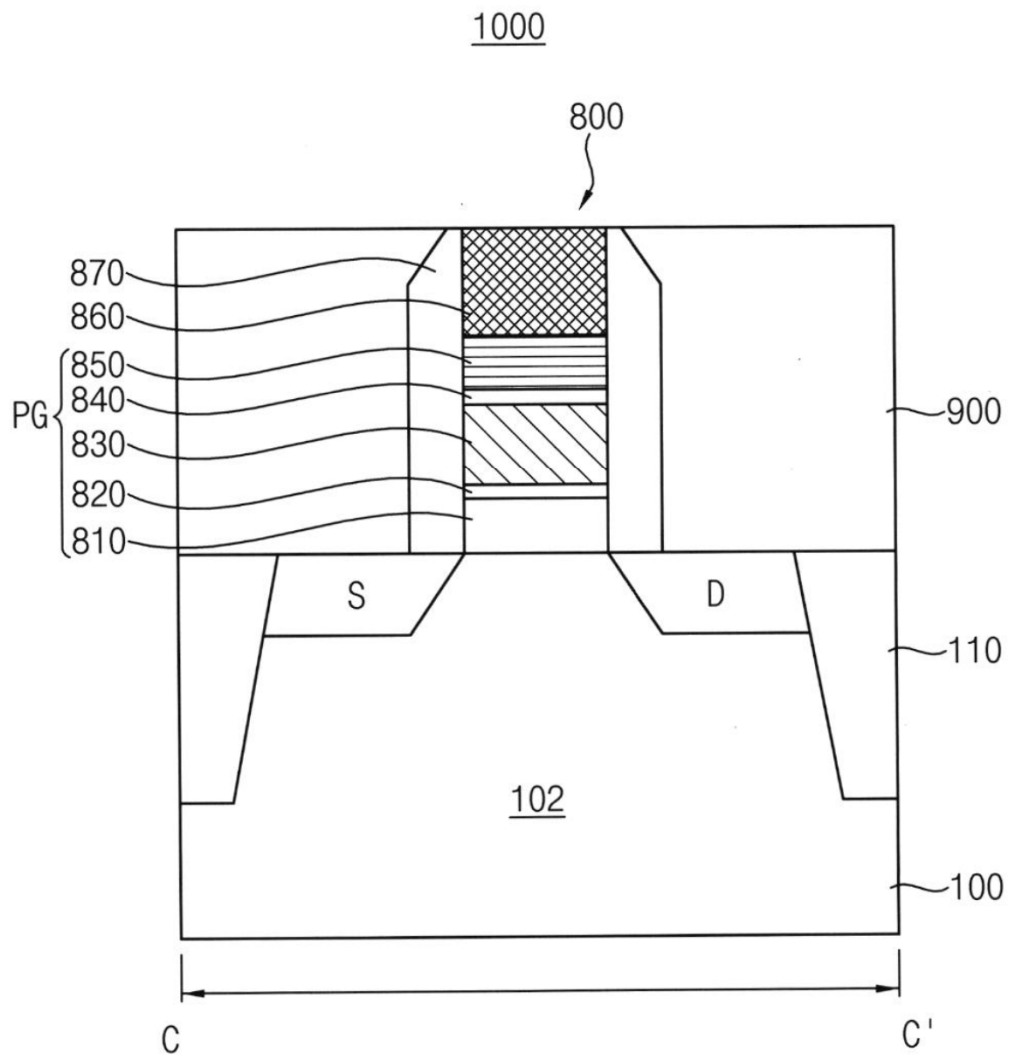


FIG. 4D

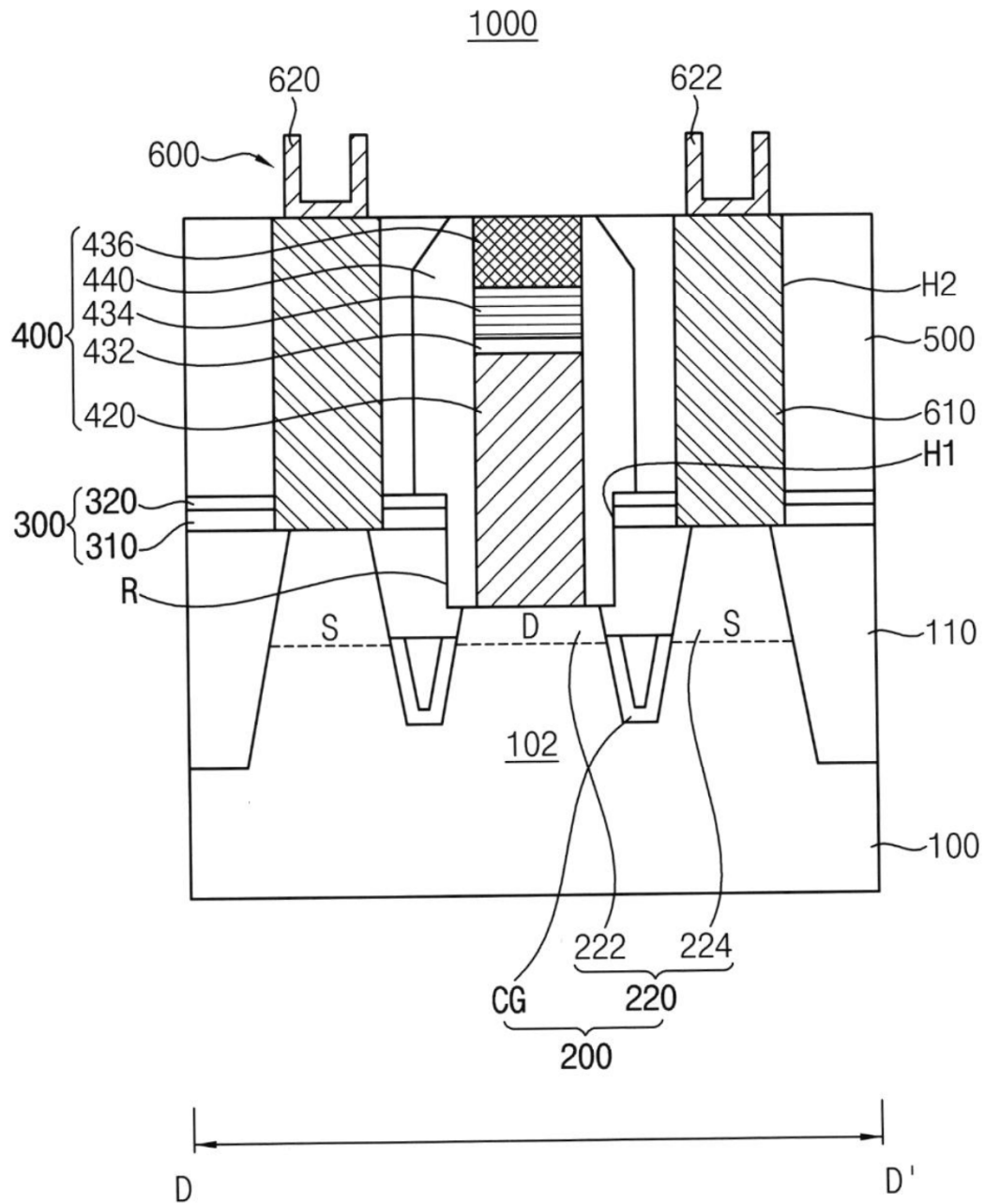


FIG. 5A

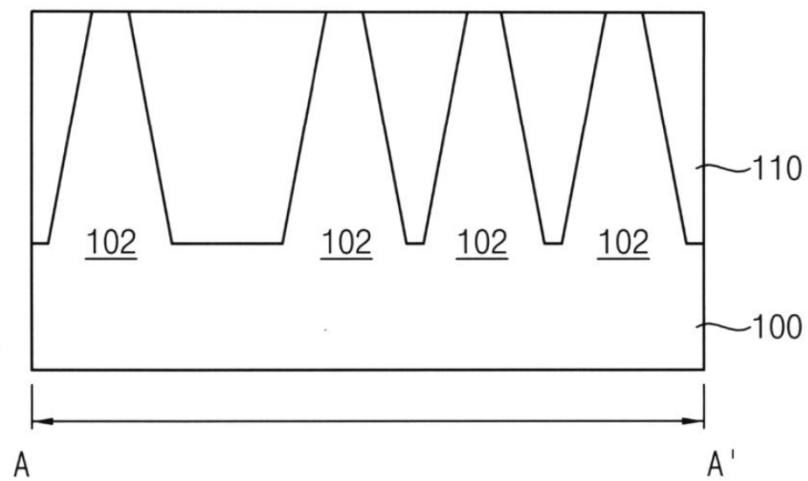


FIG. 5B

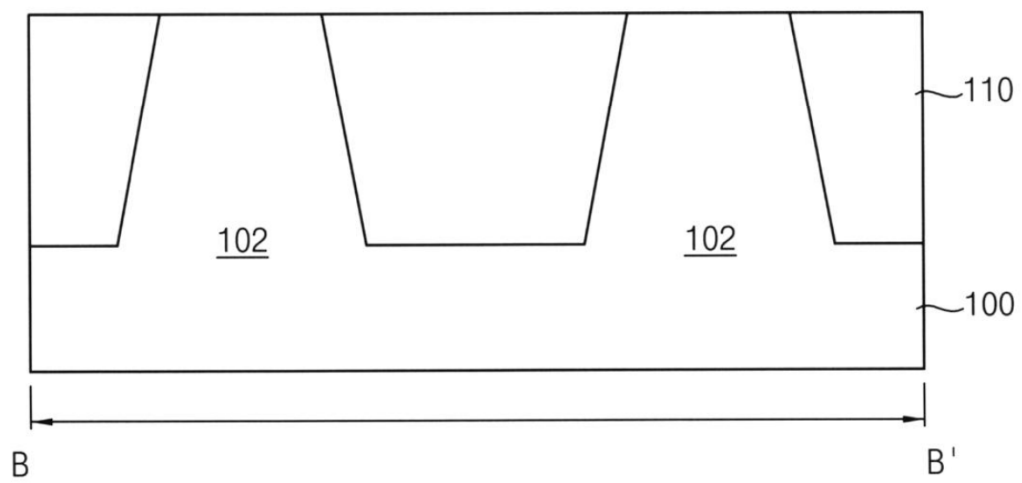


FIG. 5C

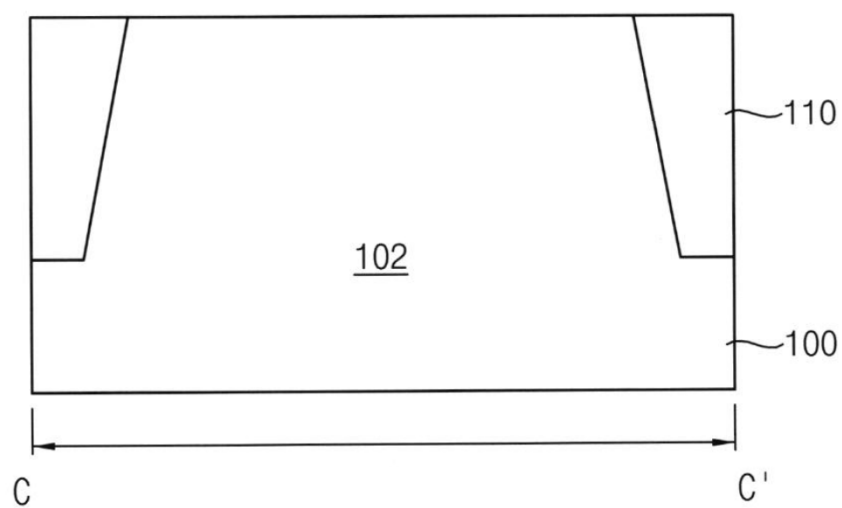


FIG. 5D

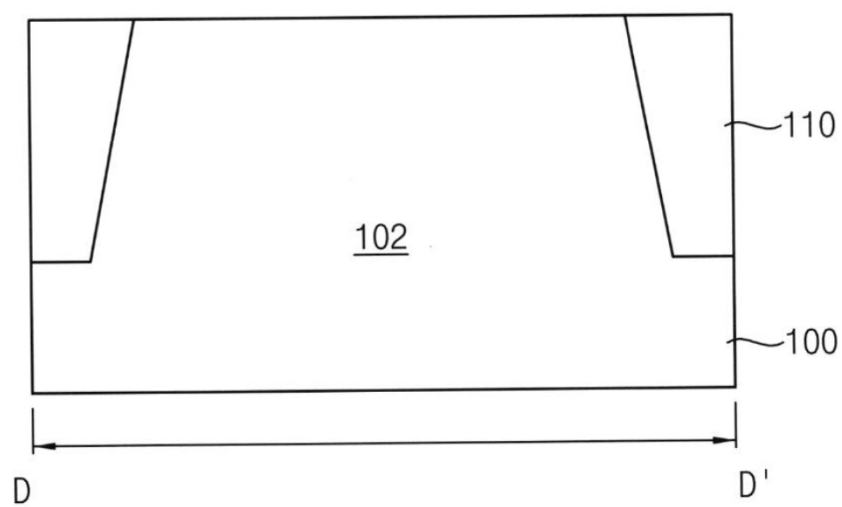


FIG. 6A

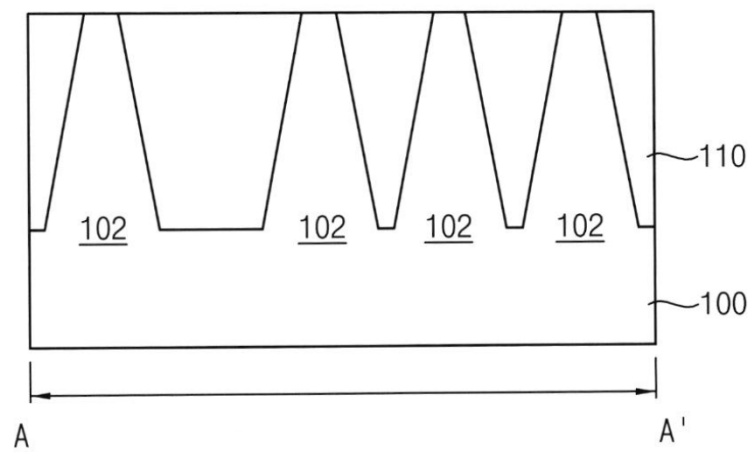


FIG. 6B

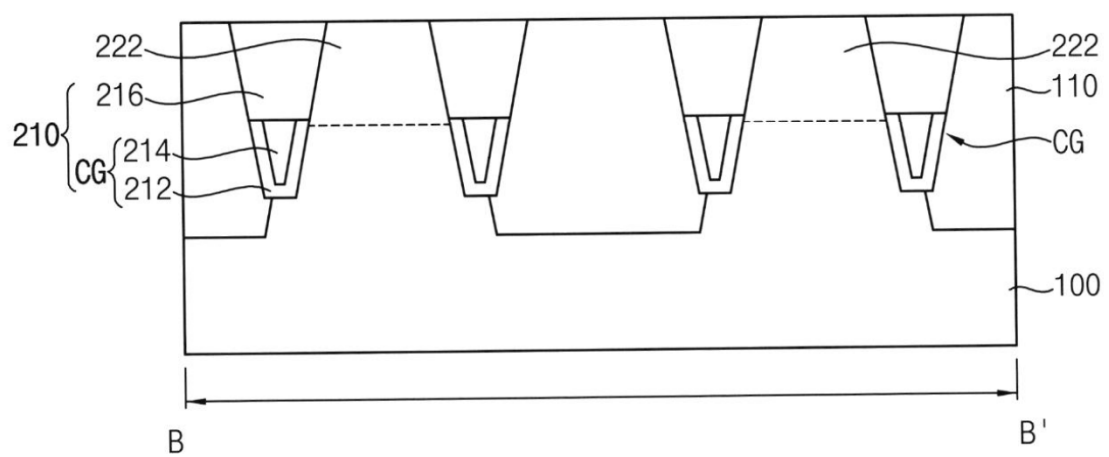


FIG. 6C

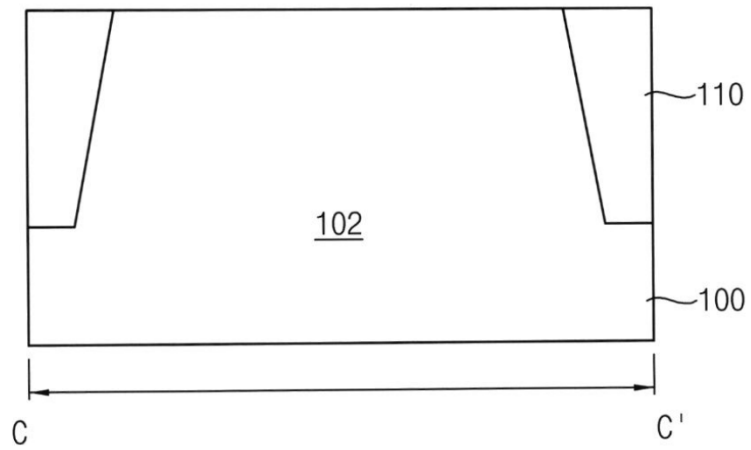


FIG. 6D

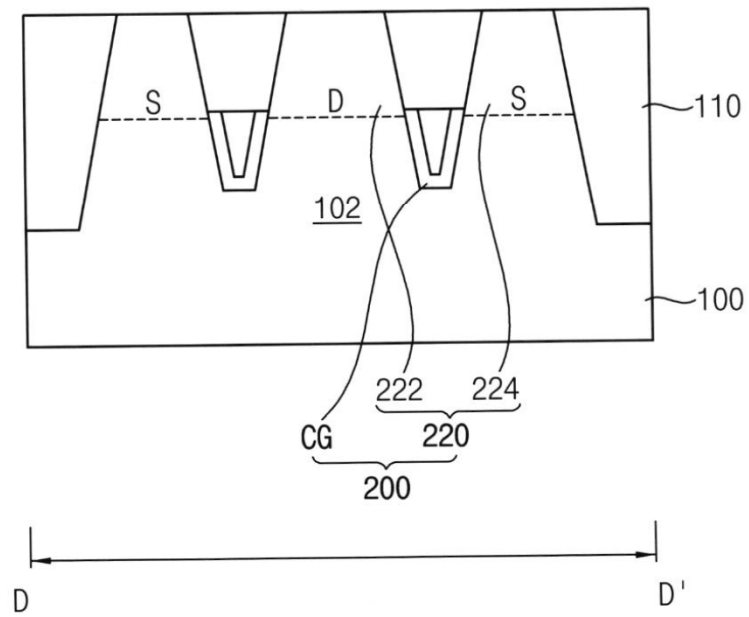


FIG. 7A

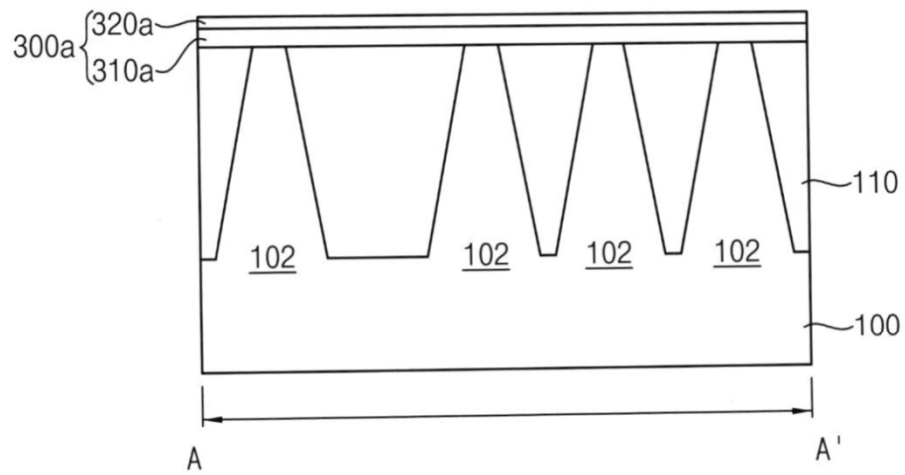


FIG. 7B

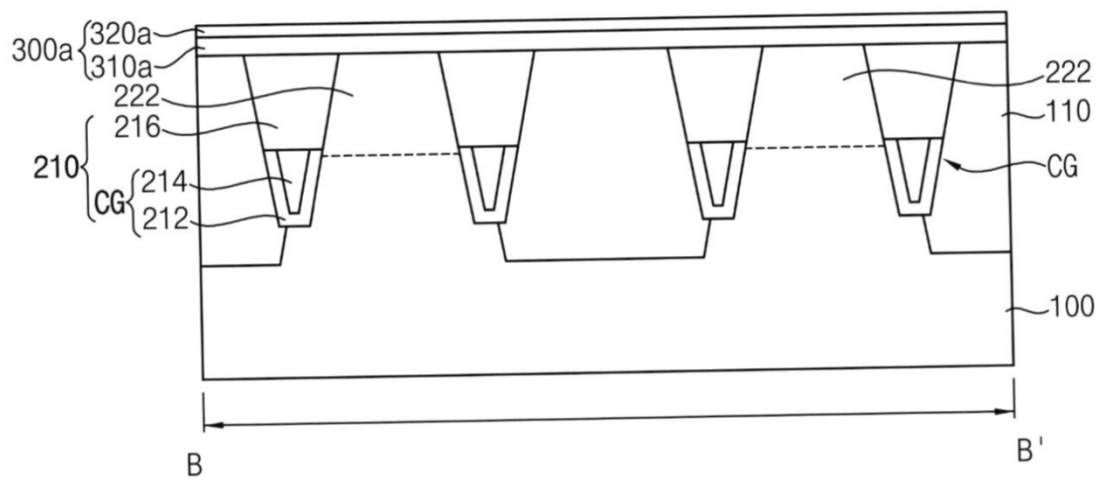


FIG. 7C

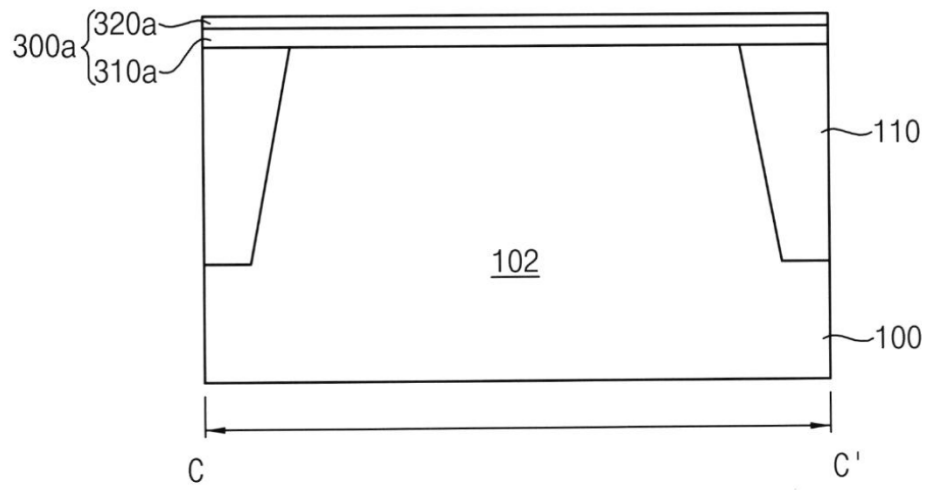


FIG. 7D

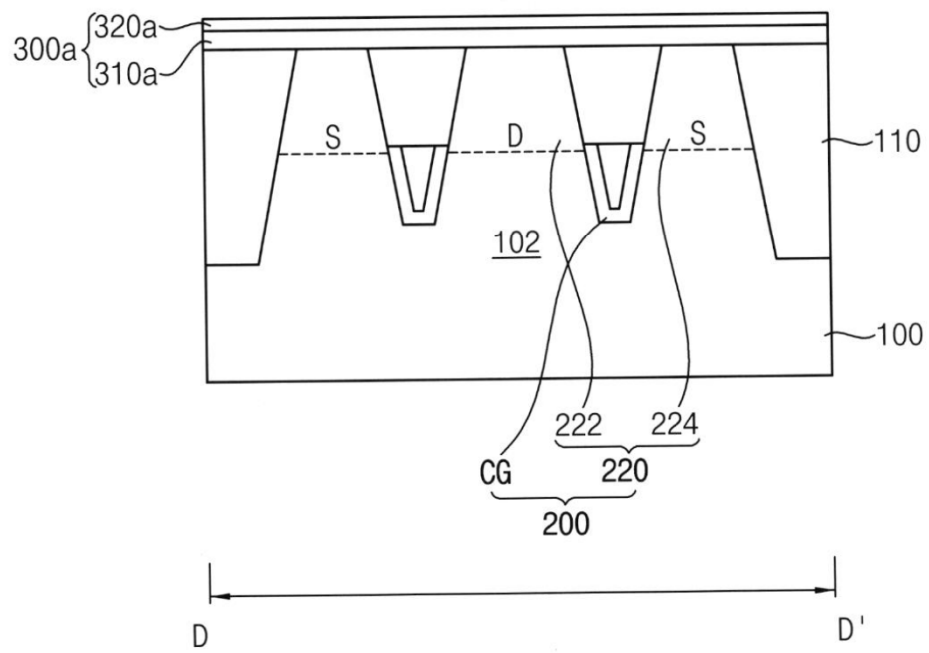


FIG. 8A

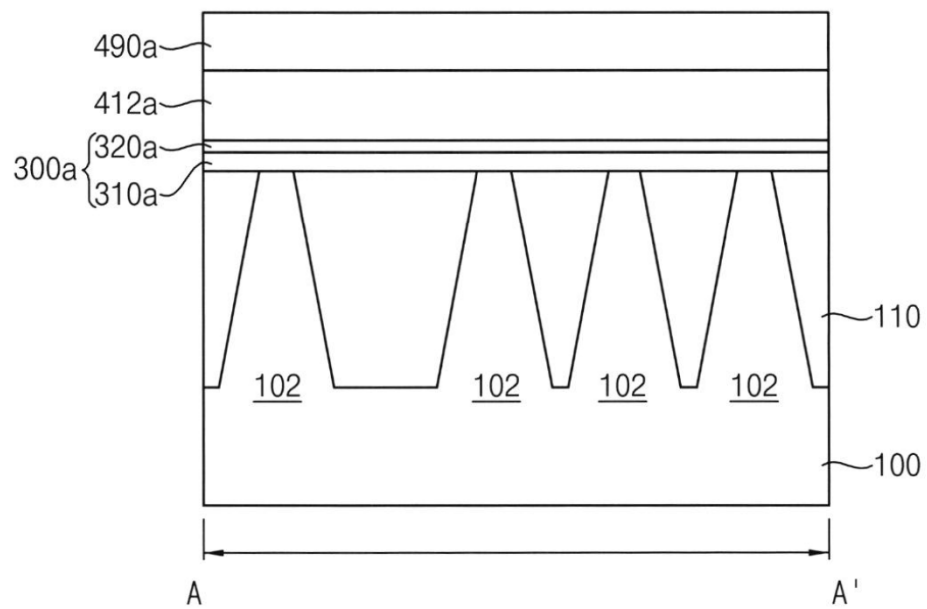


FIG. 8B

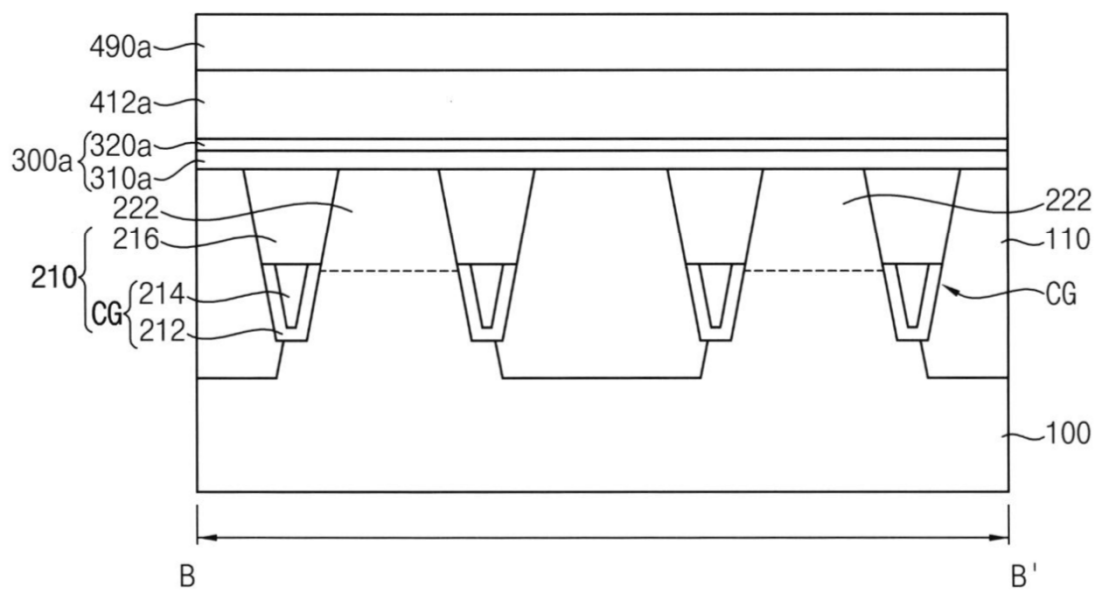


FIG. 8C

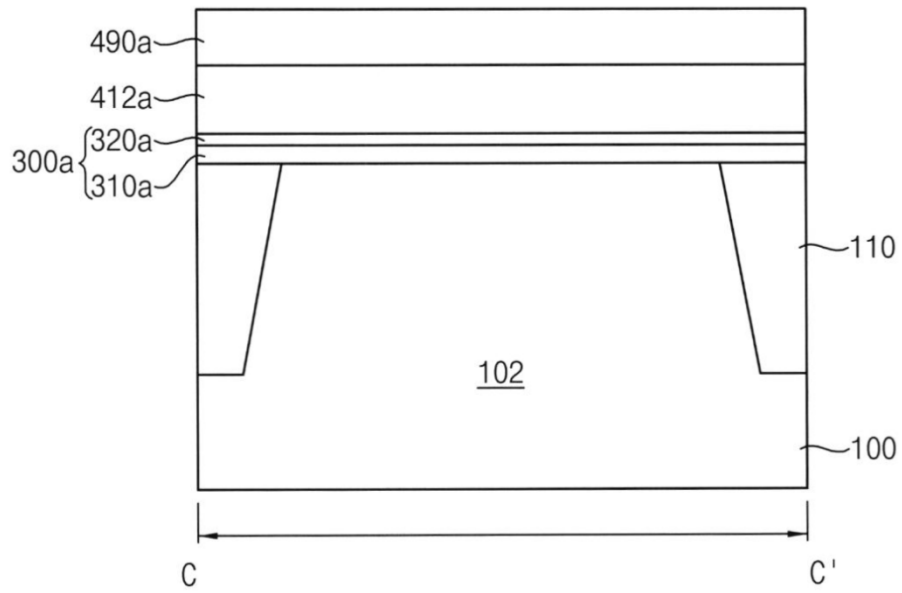


FIG. 8D

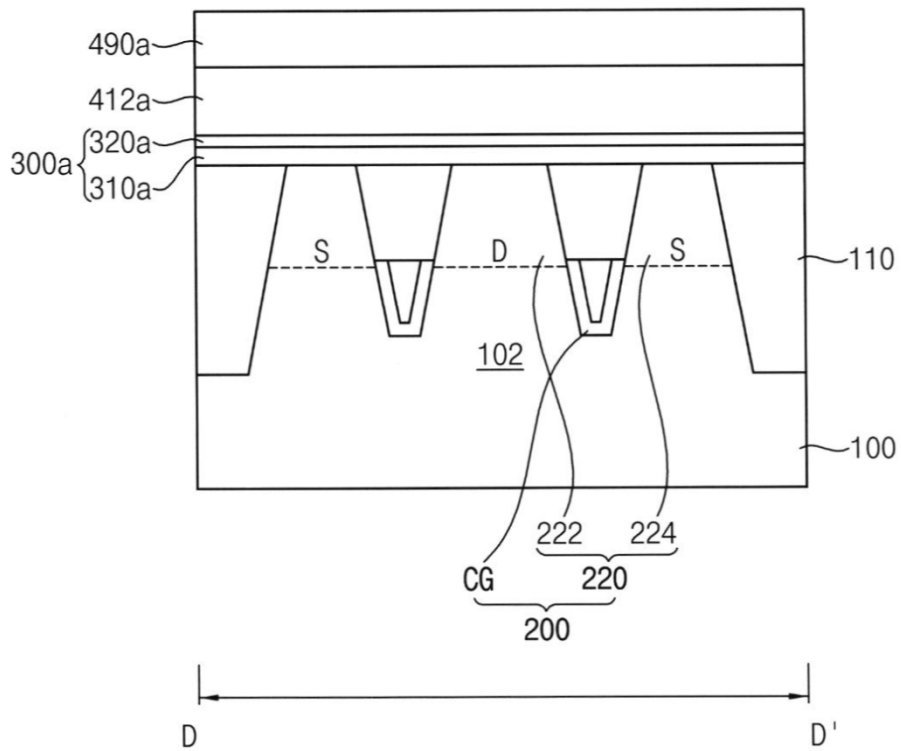


FIG. 9A

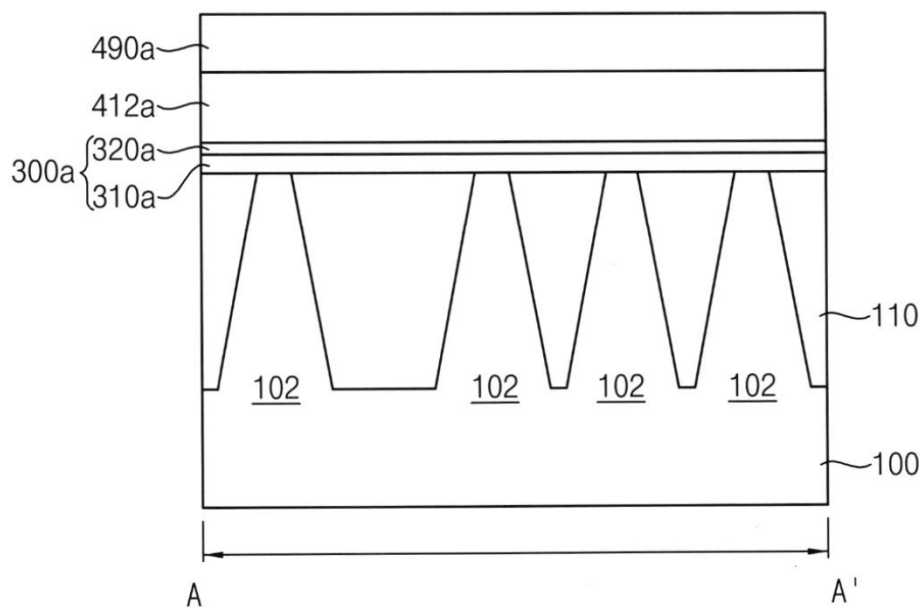


FIG. 9B

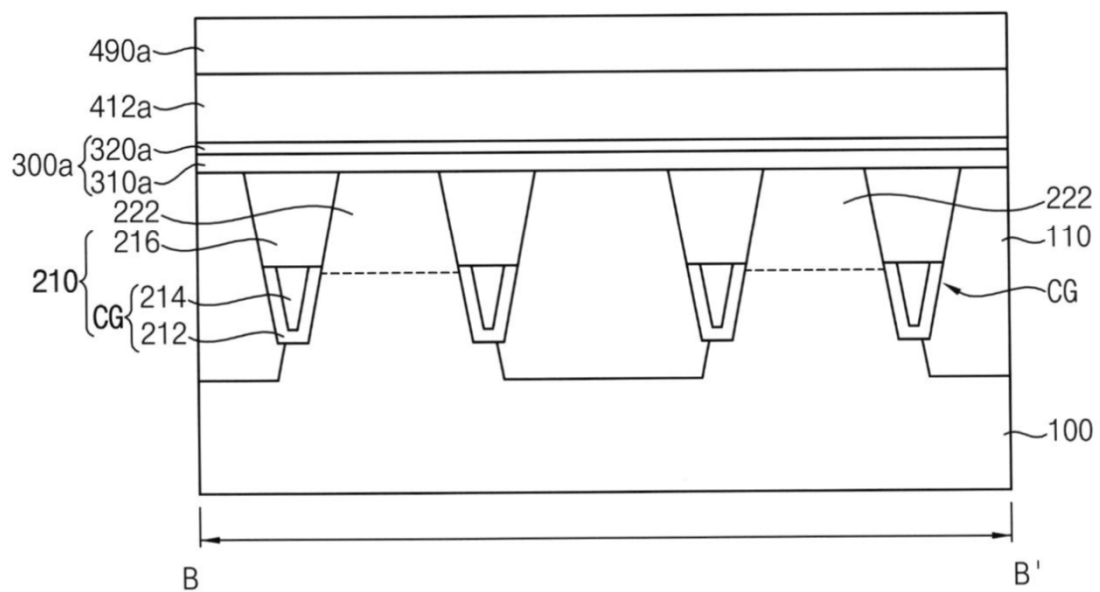


FIG. 9C

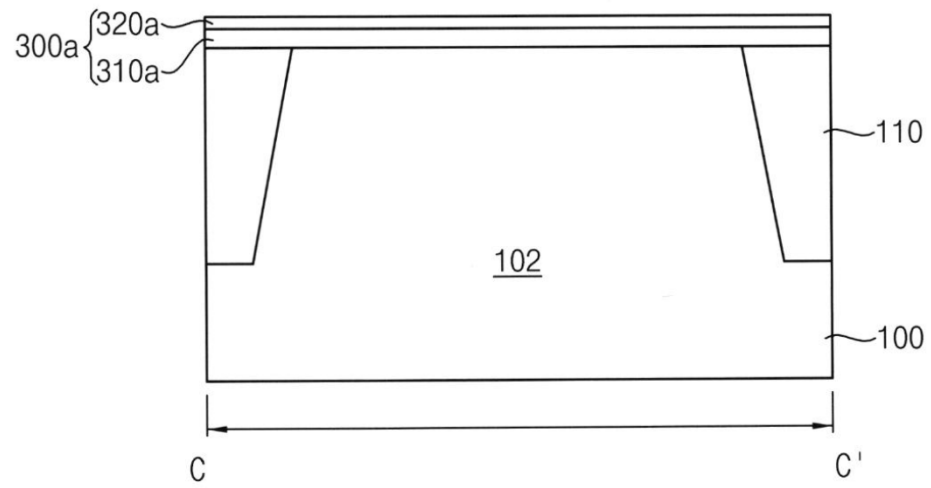


FIG. 9D

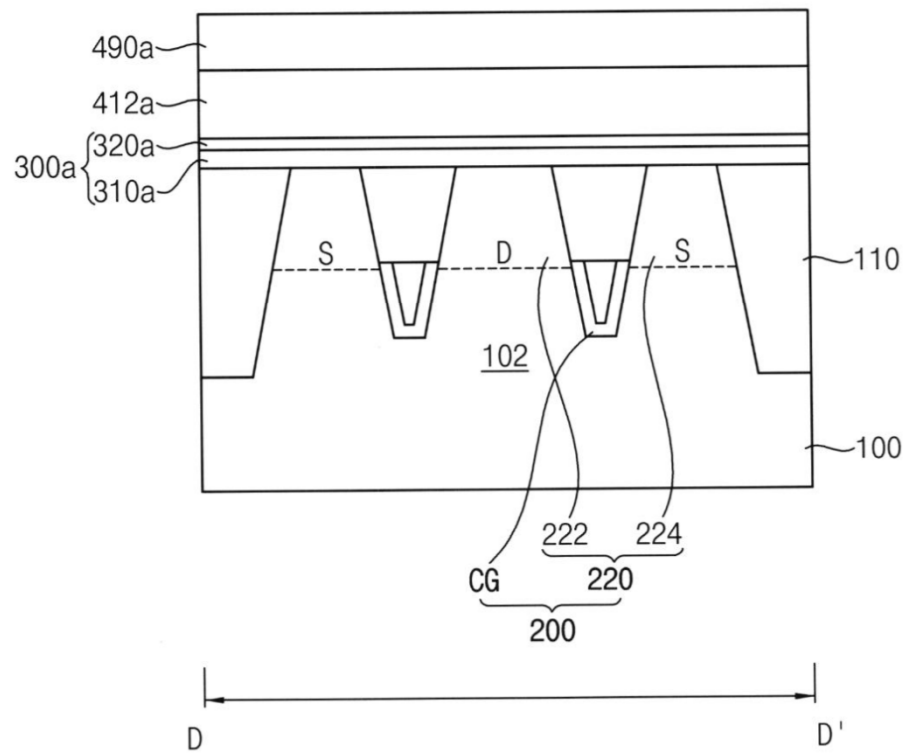


FIG. 10A

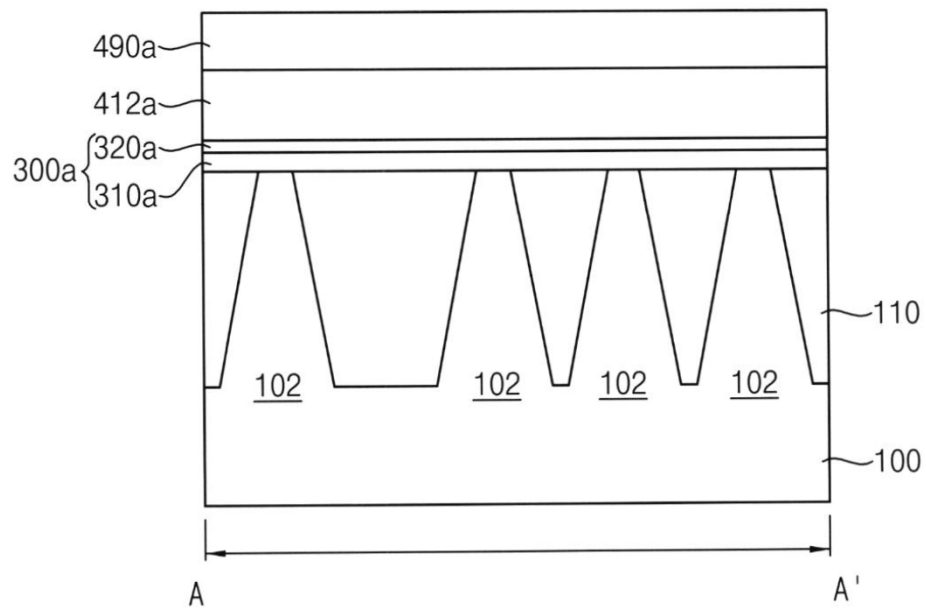


FIG. 10B

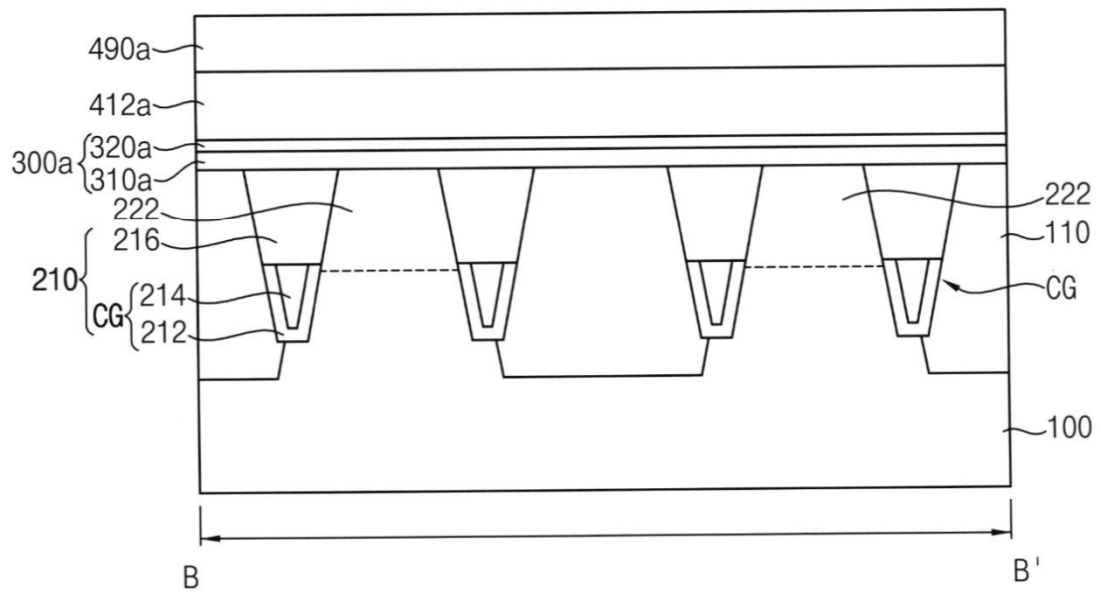


FIG. 10C

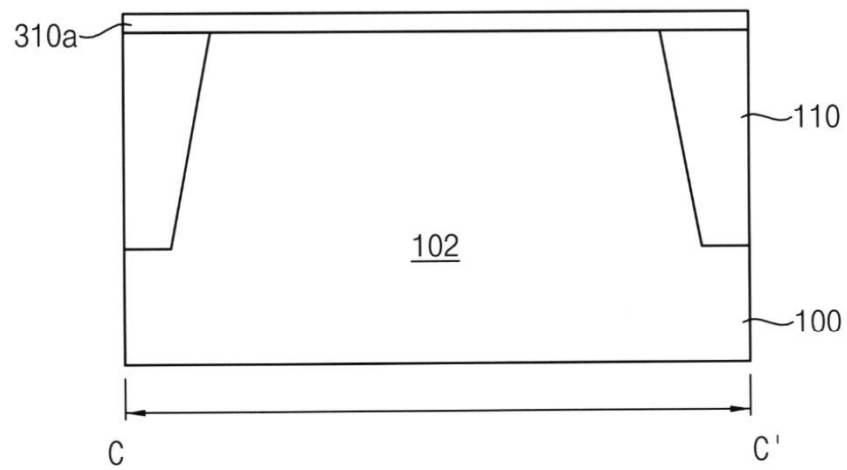


FIG. 10D

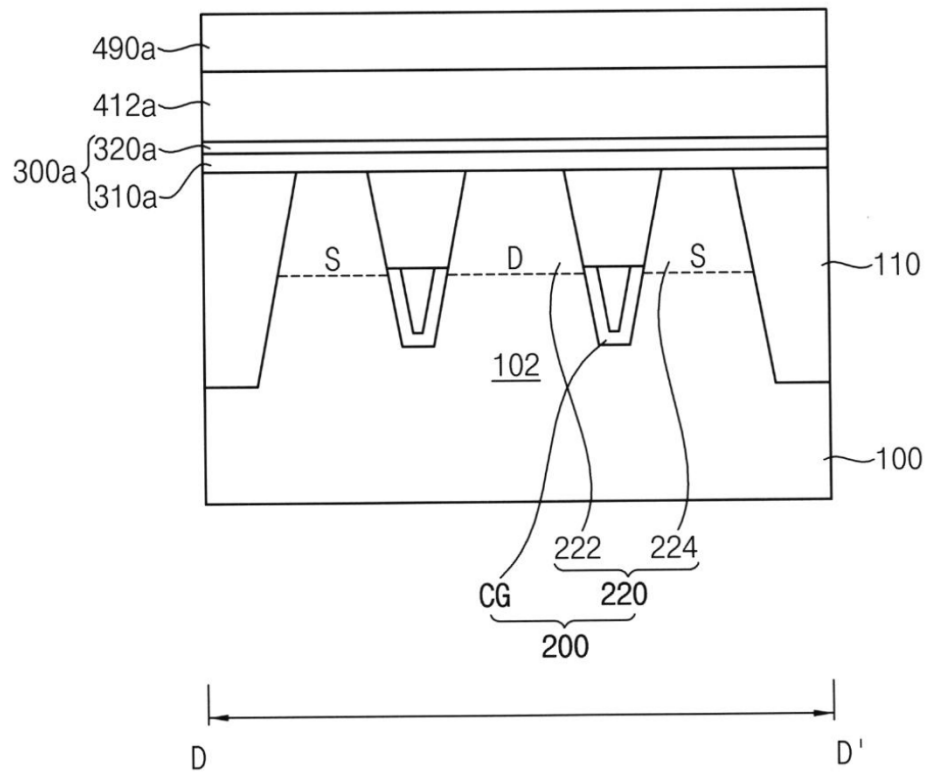


FIG. 11A

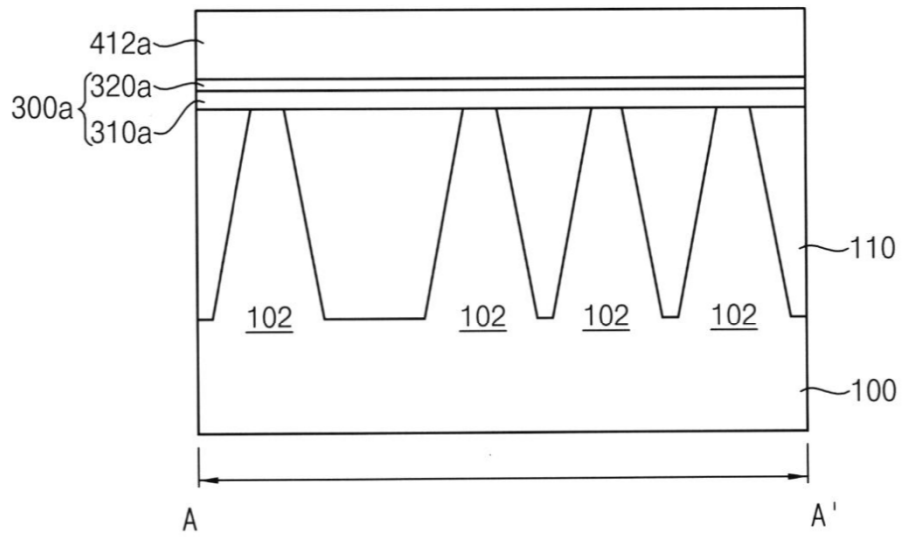


FIG. 11B

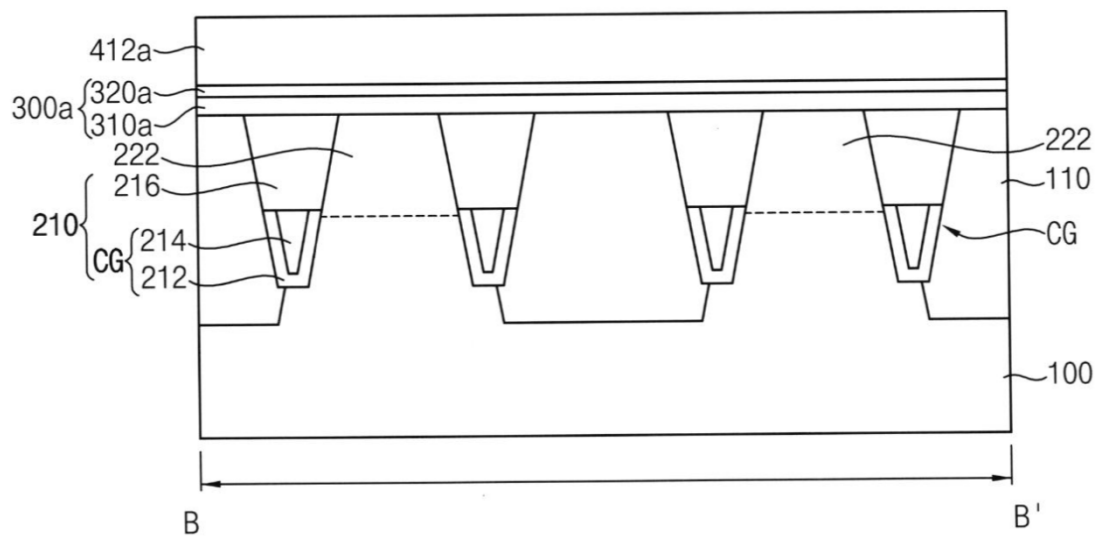


FIG. 11C

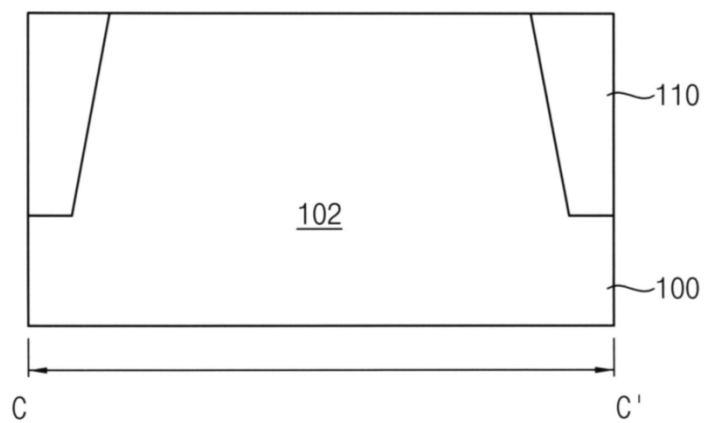


FIG. 11D

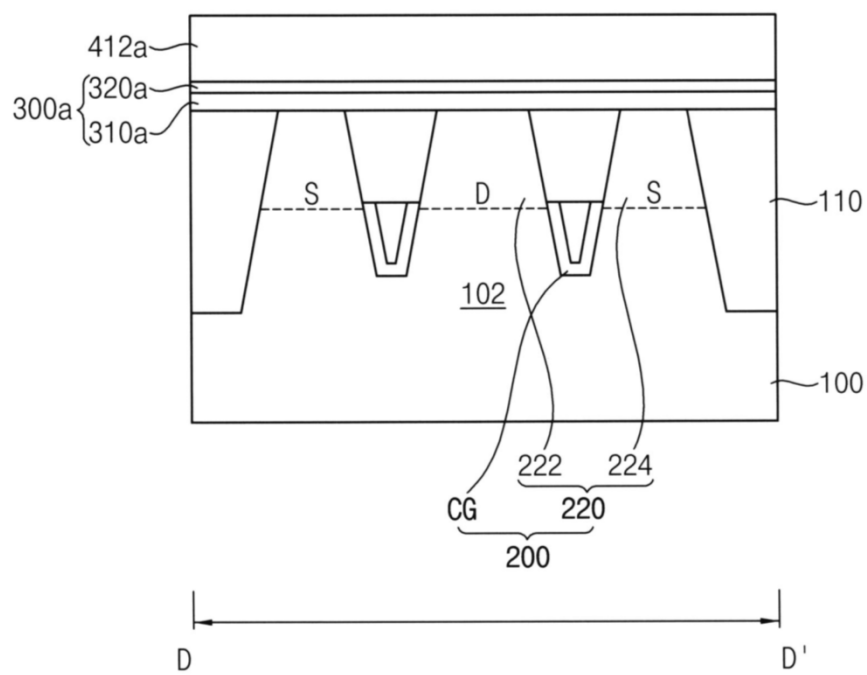


FIG. 12A

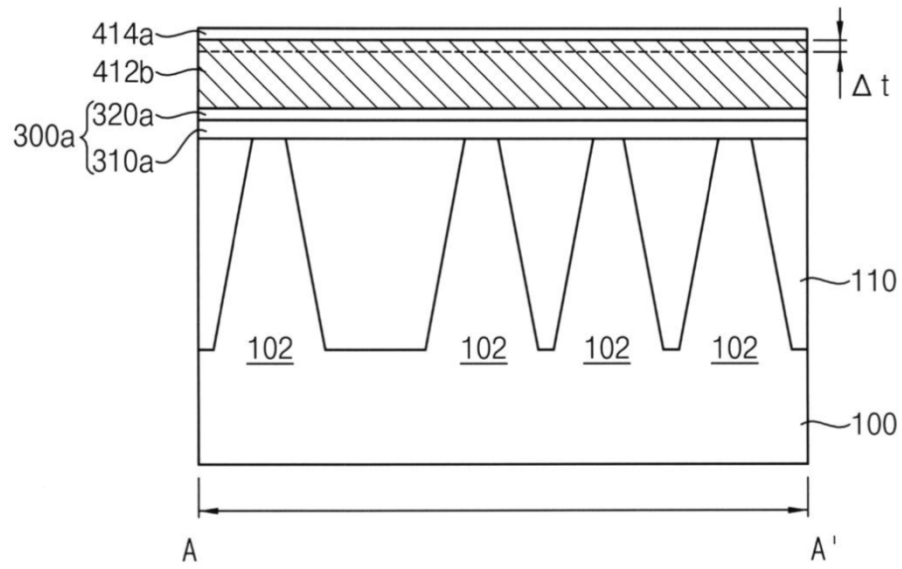


FIG. 12B

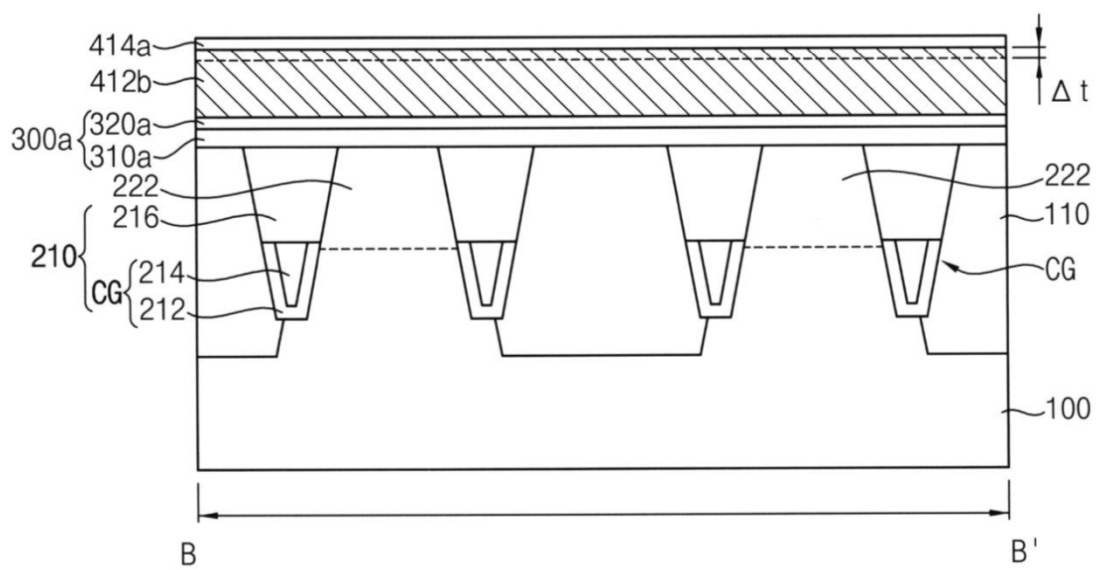


FIG. 12C

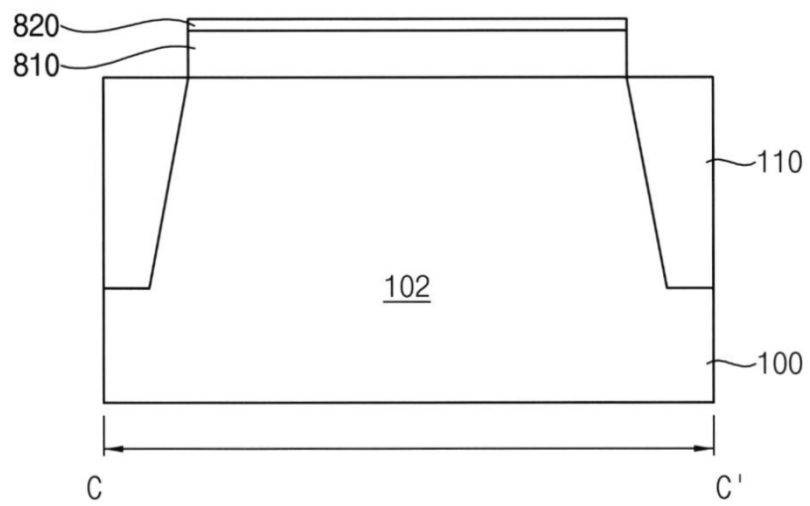


FIG. 12D

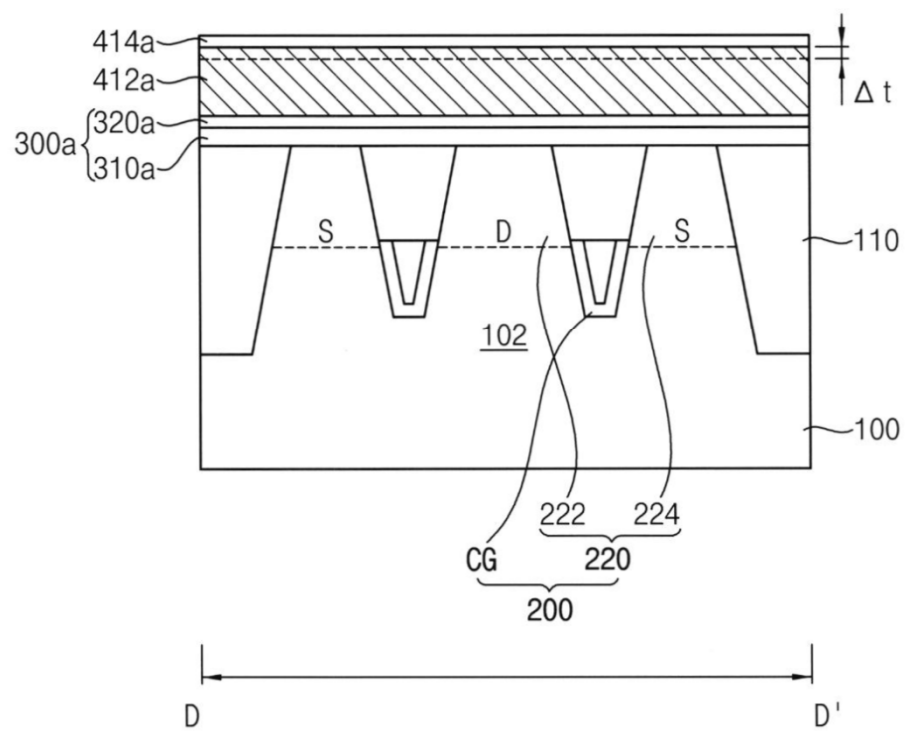


FIG. 13A

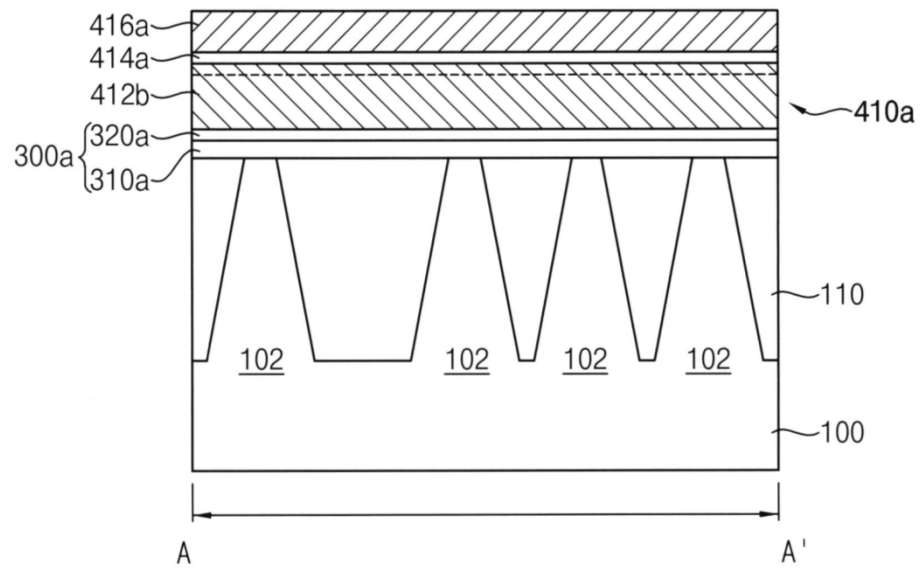


FIG. 13B

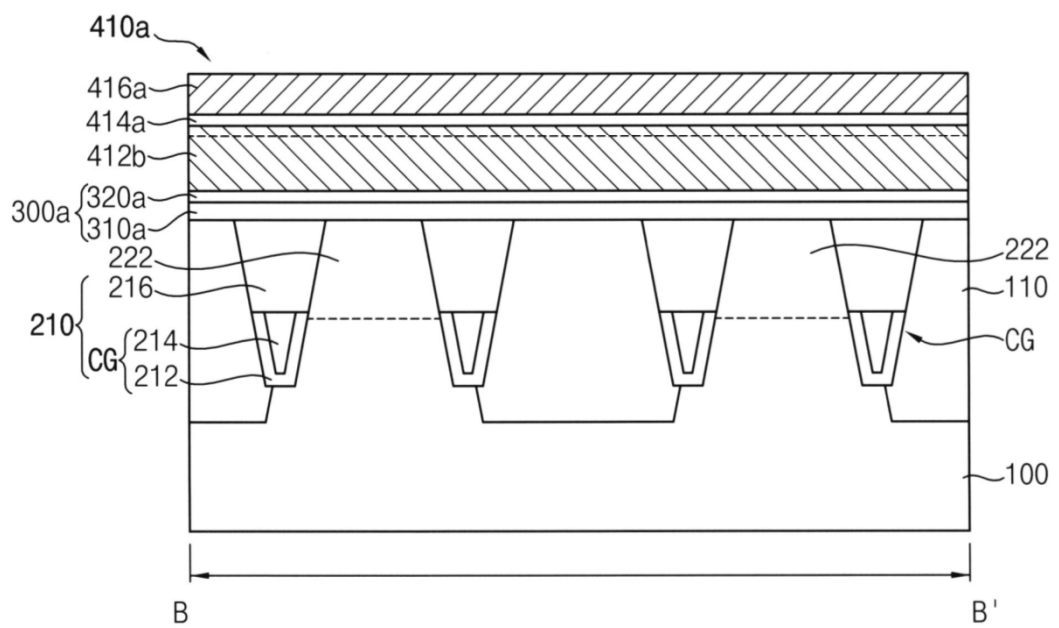


FIG. 13C

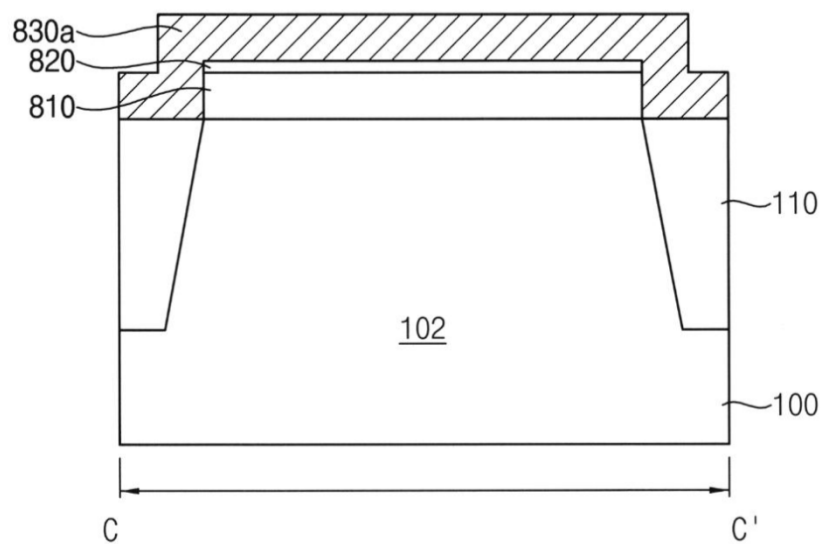
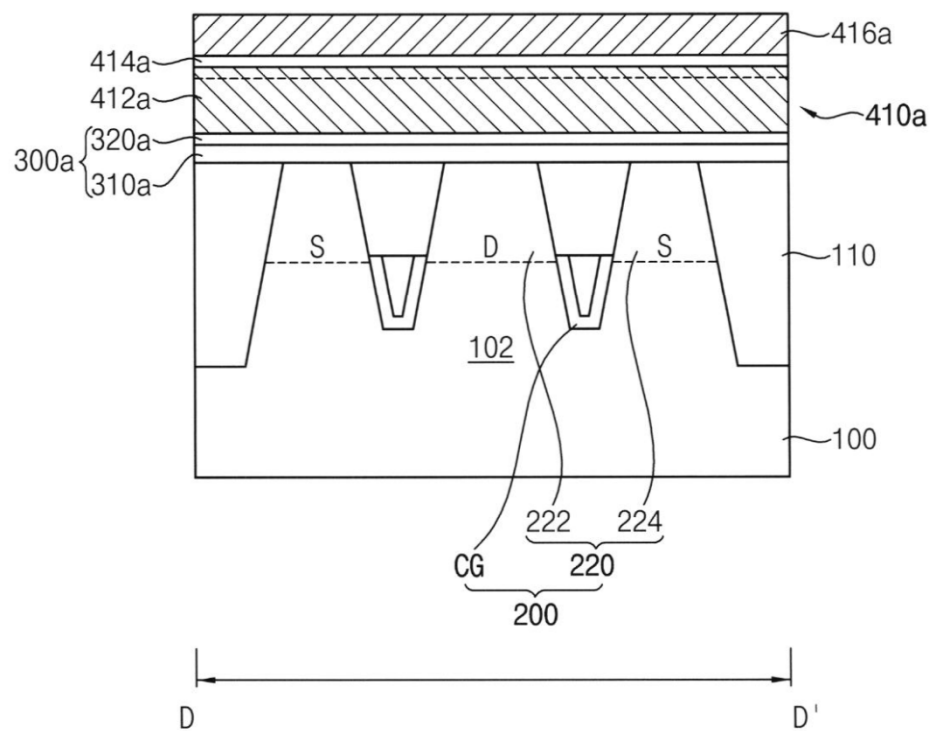


FIG. 13D



This cross-sectional view shows a substrate 100 with a series of trapezoidal patterns 102. A layer 110 is deposited over the substrate, with a thickness d indicated. A layer 300 is formed on top of layer 110, consisting of sub-layers 310 and 320. A layer 410b is formed on top of layer 300, with sub-layers 412c, 414b, and 416b. A gap H1 is formed between the patterns 102. A dimension R is indicated for the width of the patterns 102. The cross-section is taken along line A-A'.

Diagram illustrating a cross-sectional view of a semiconductor device structure. The structure includes a substrate 100 with a trench 110. A gate stack 300 is formed on the trench walls, including layers 310, 320, 412c, and 414b. A channel layer 102 is formed in the trench, with regions 222 and 224. A contact layer 416b is formed on top of the gate stack. The device is shown in a cross-section with dimensions D and D'.

FIG. 15A

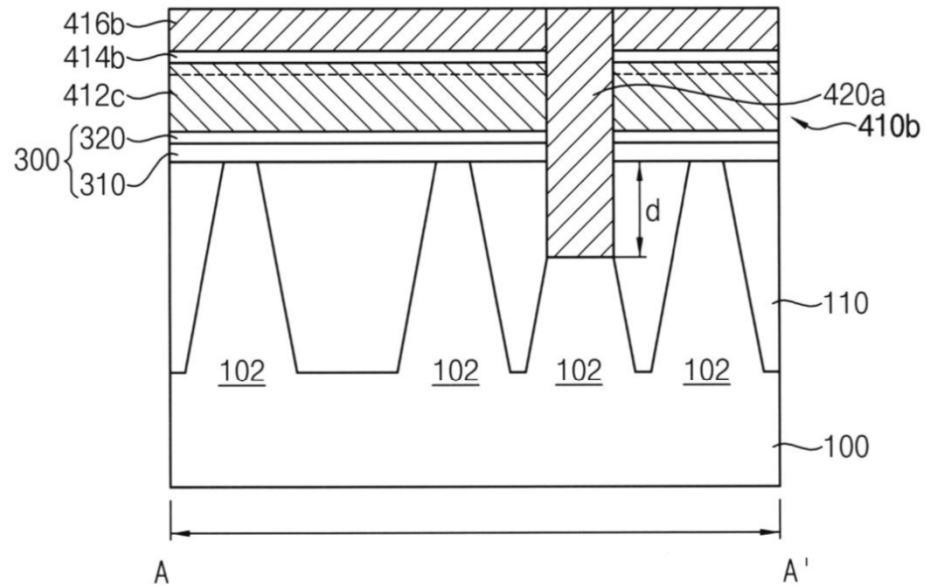


FIG. 15B

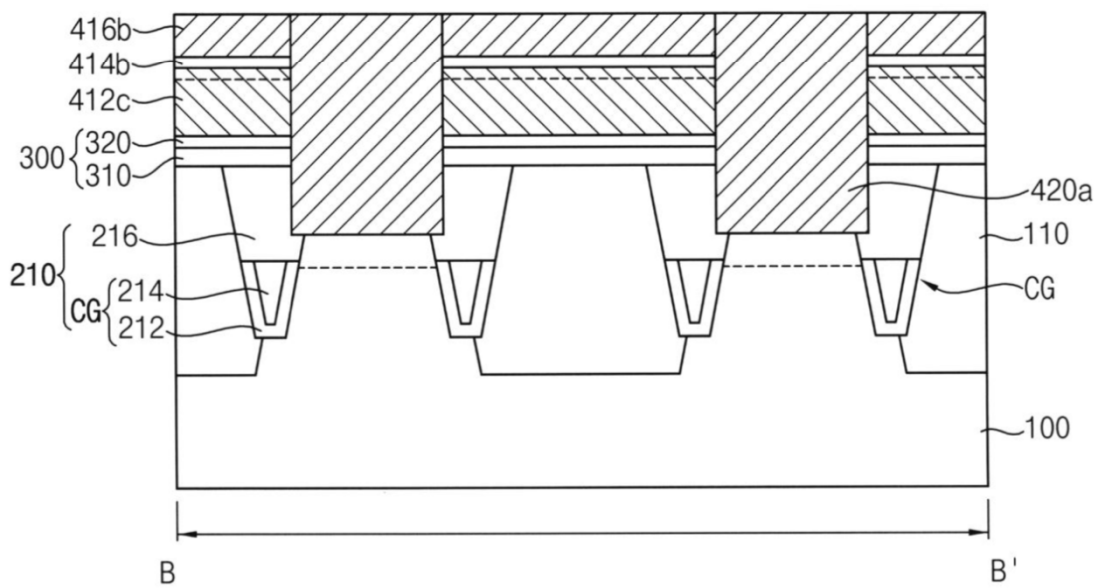


FIG. 15C

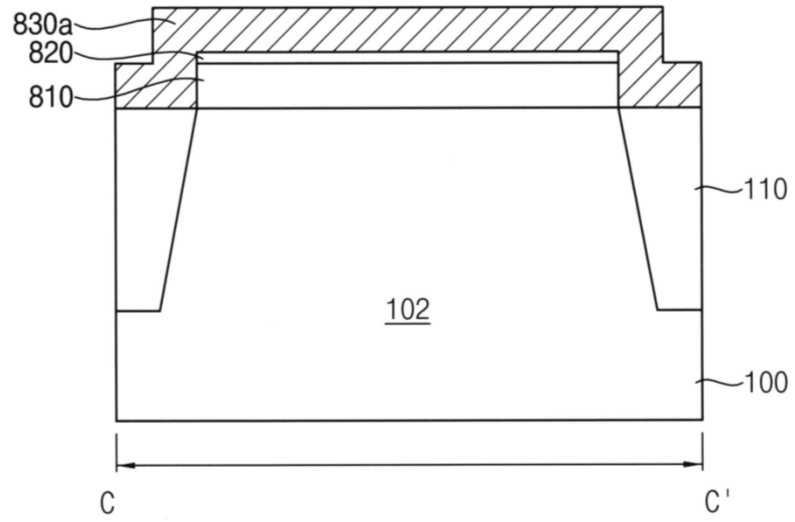


FIG. 15D

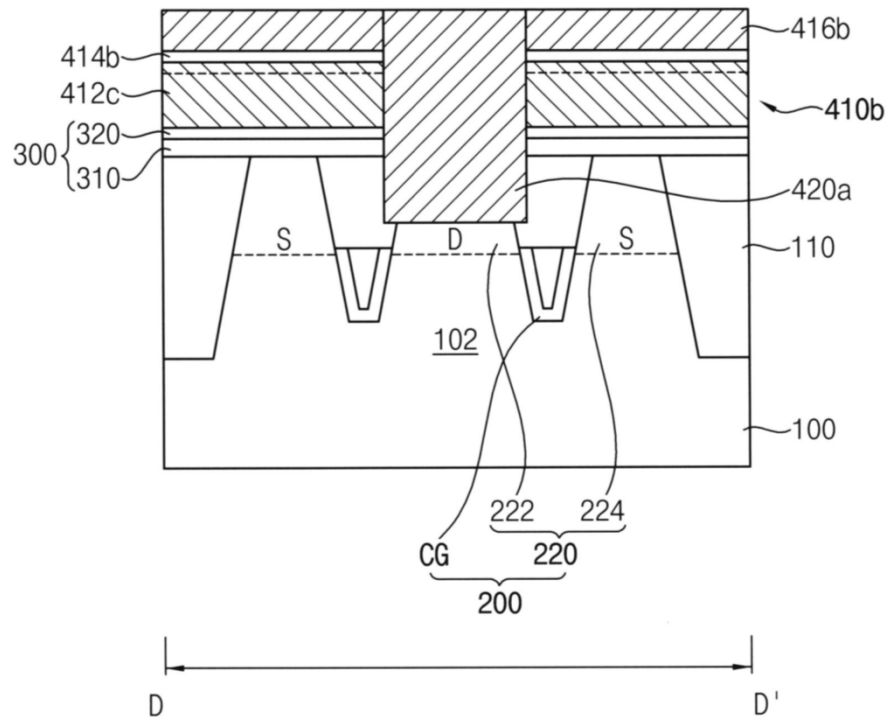


FIG. 16A

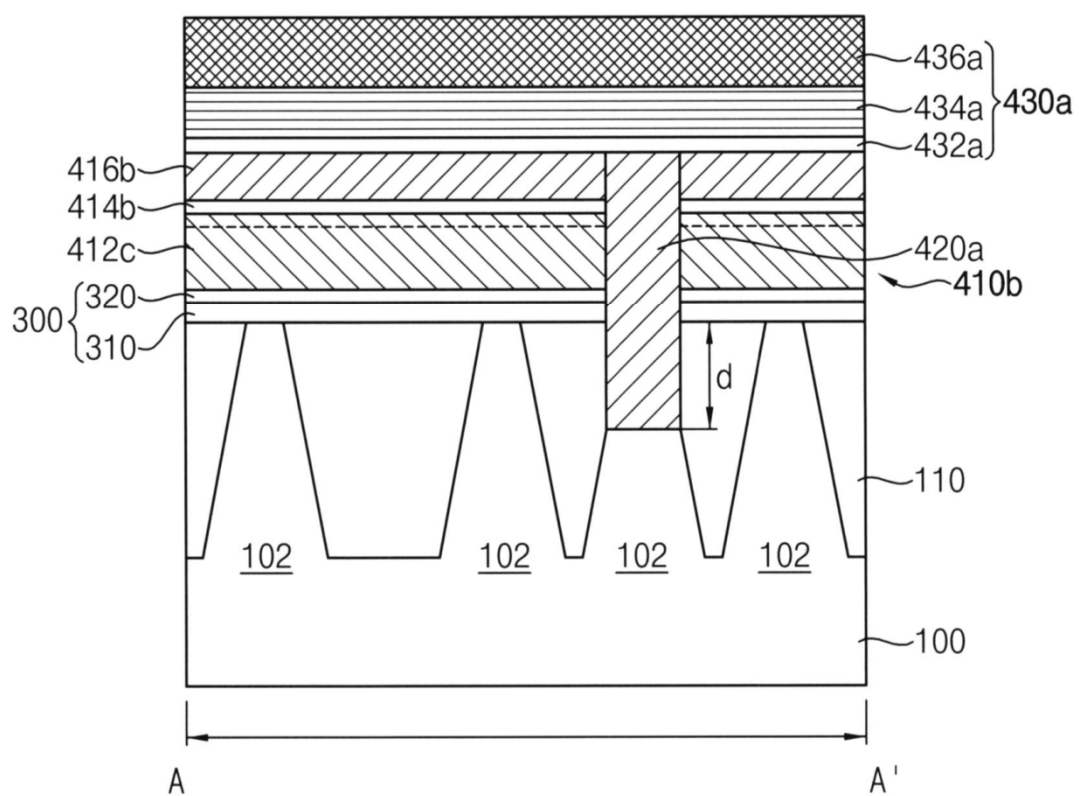


FIG. 16B

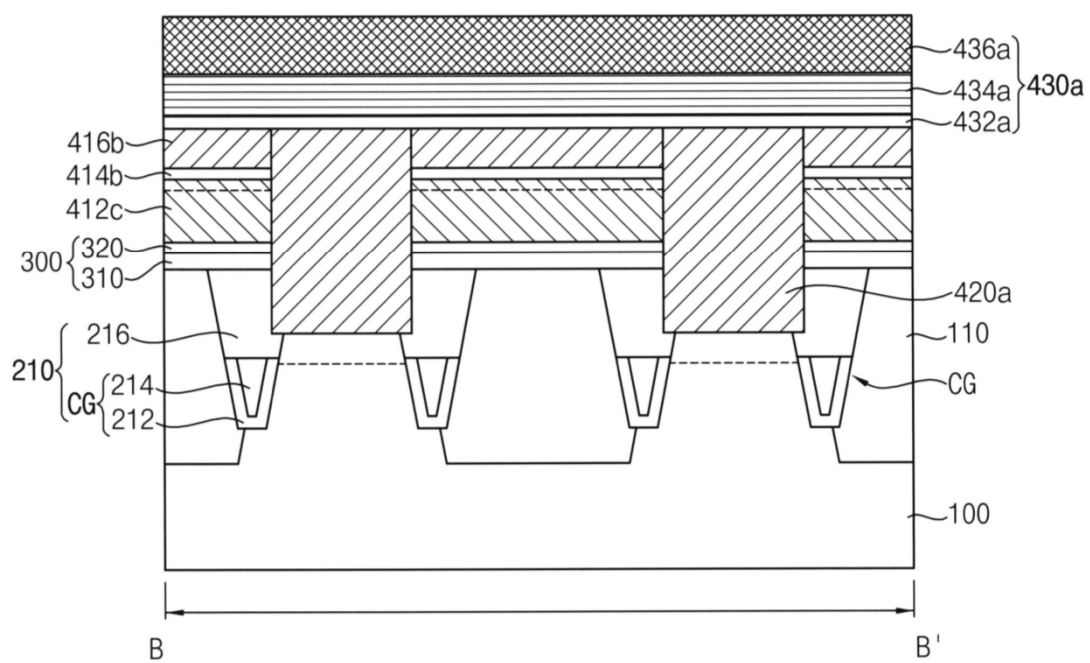


FIG. 16C

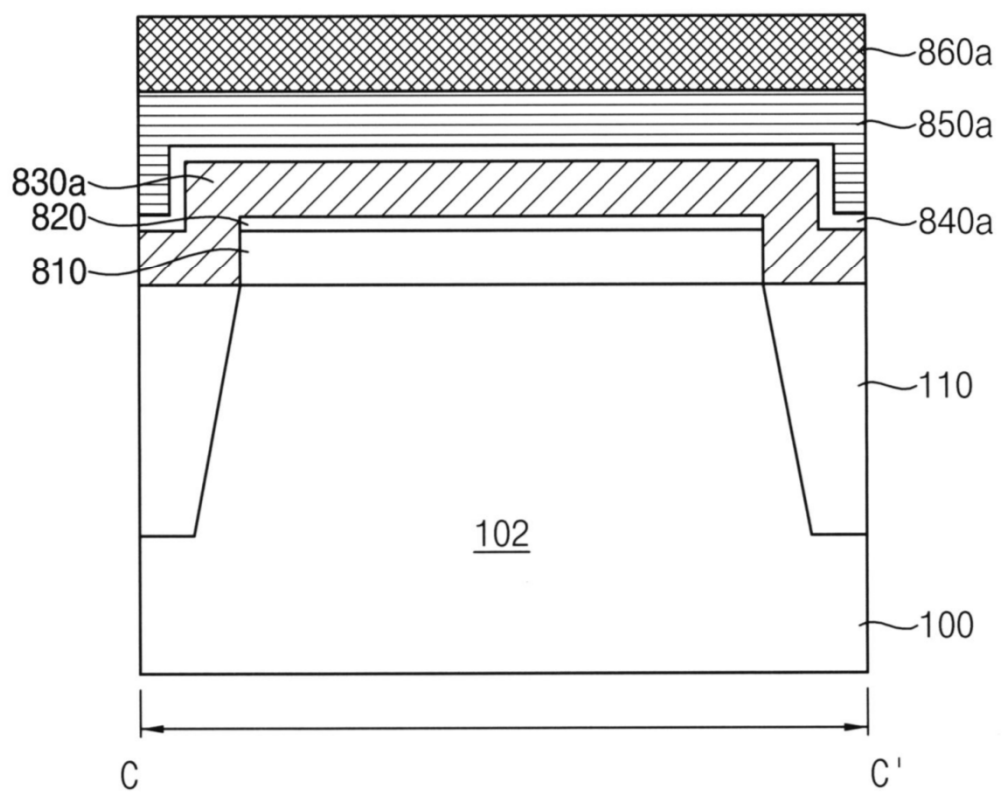


FIG. 16D

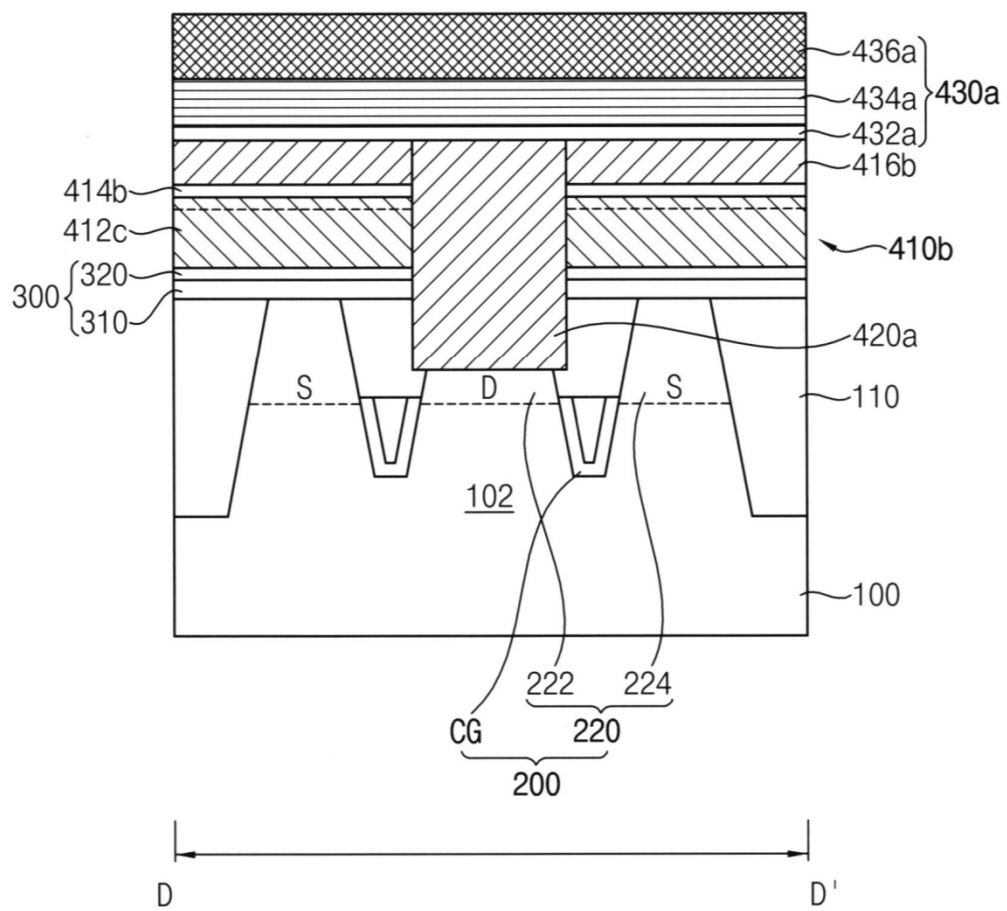


FIG. 17A

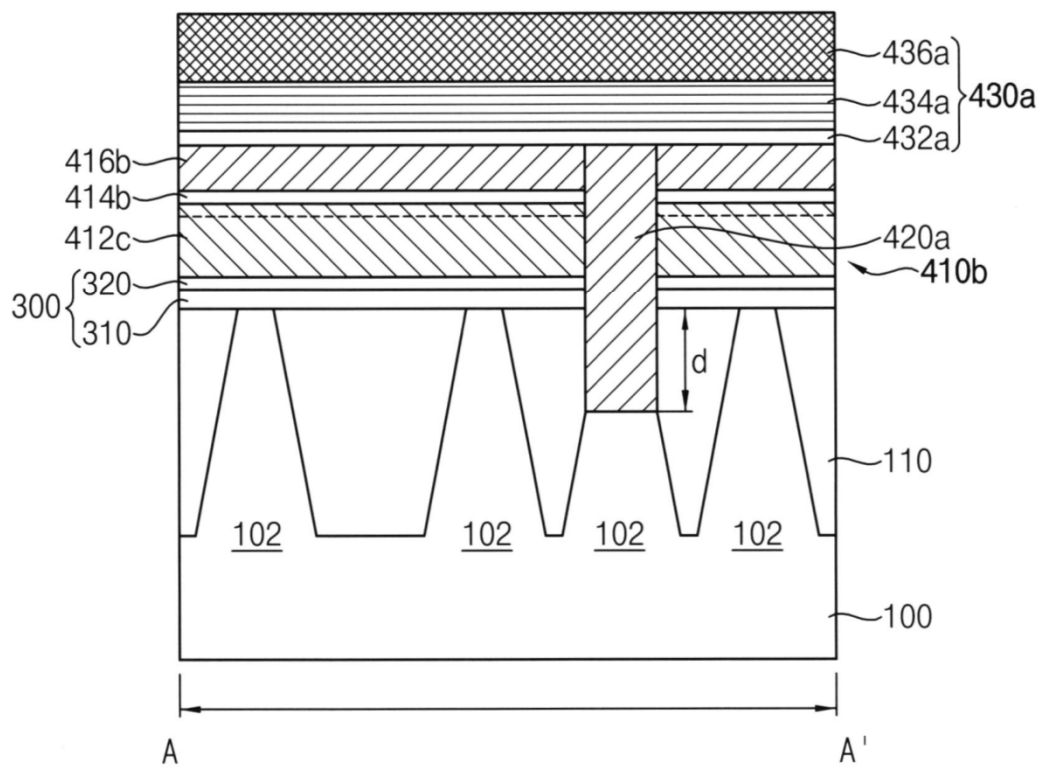


FIG. 17B

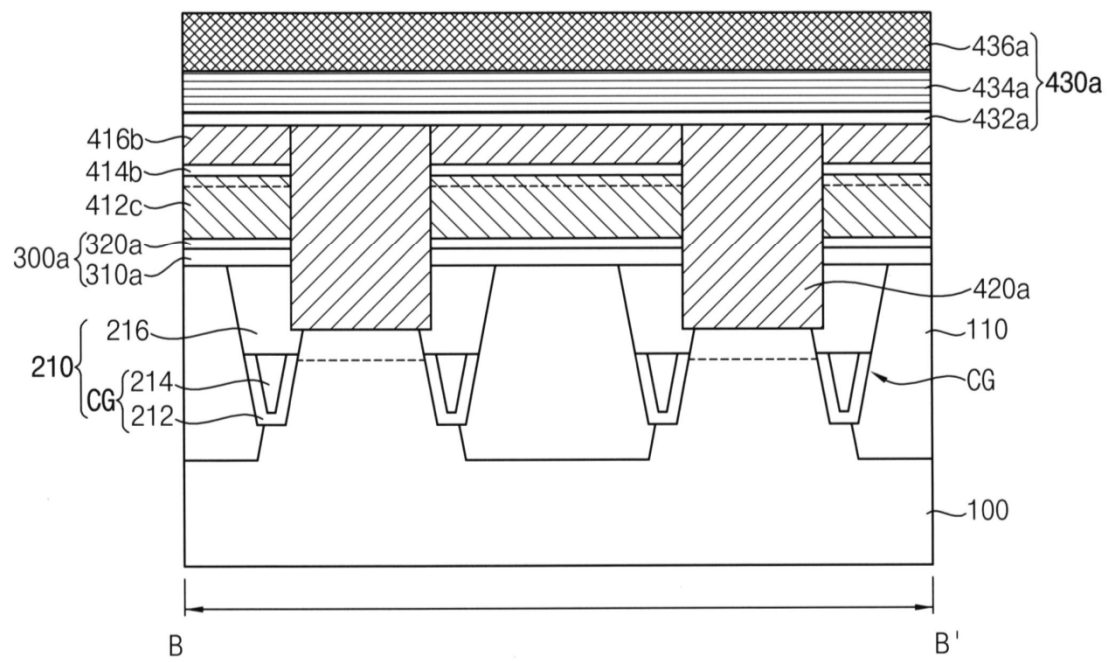


FIG. 17C

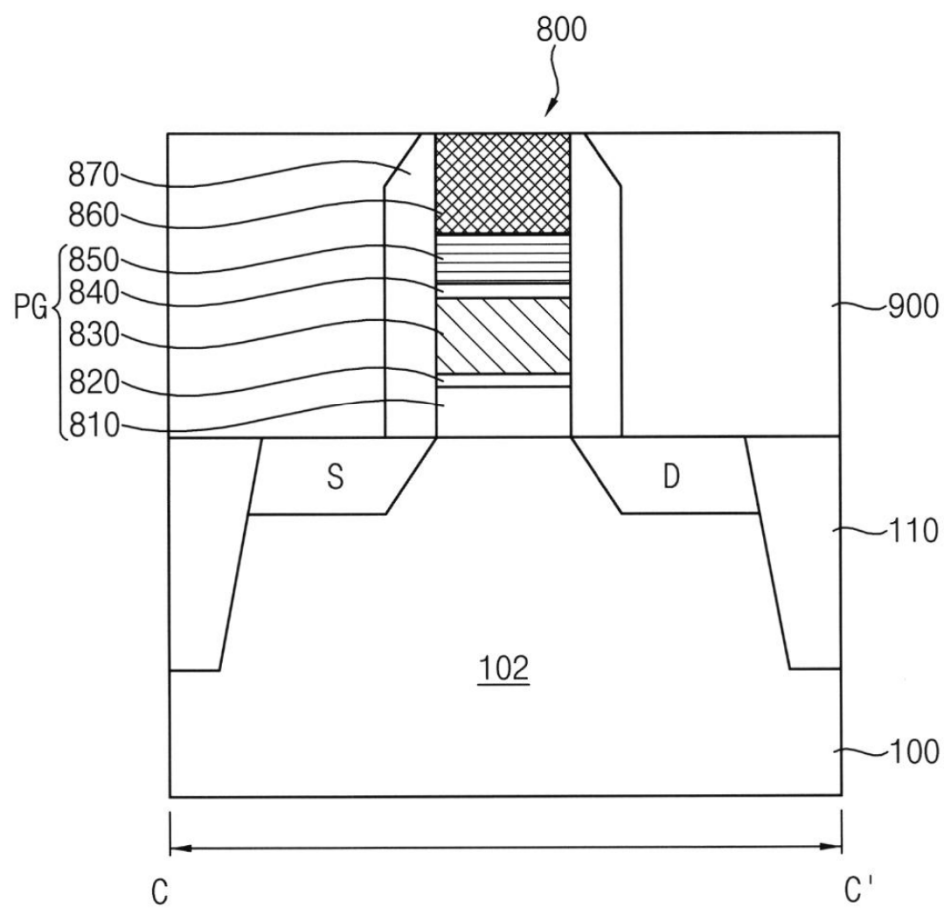


FIG. 17D

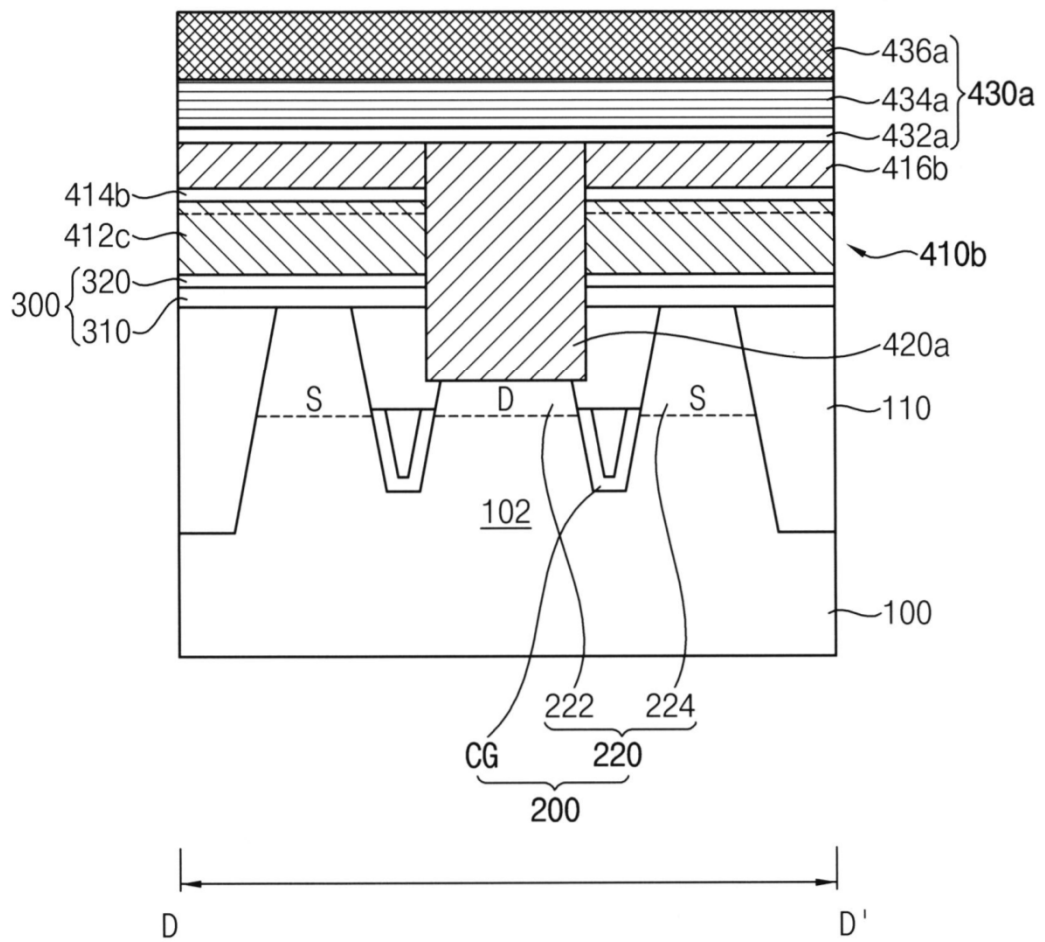


FIG. 18A

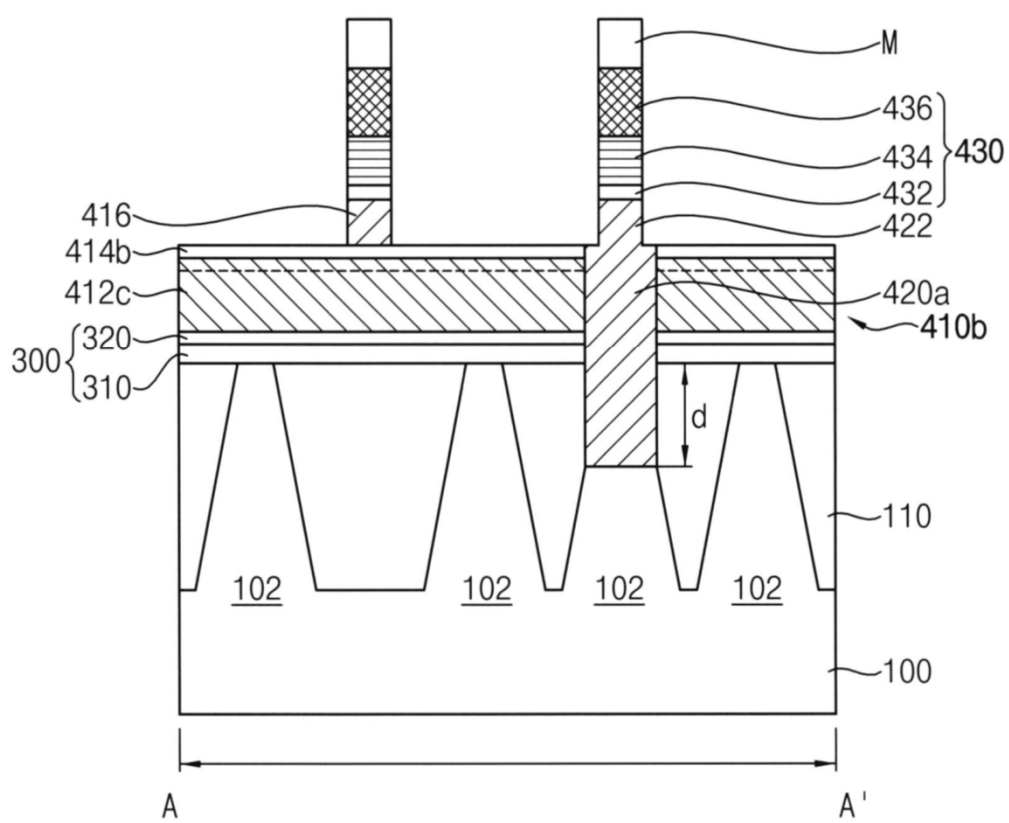


FIG. 18B

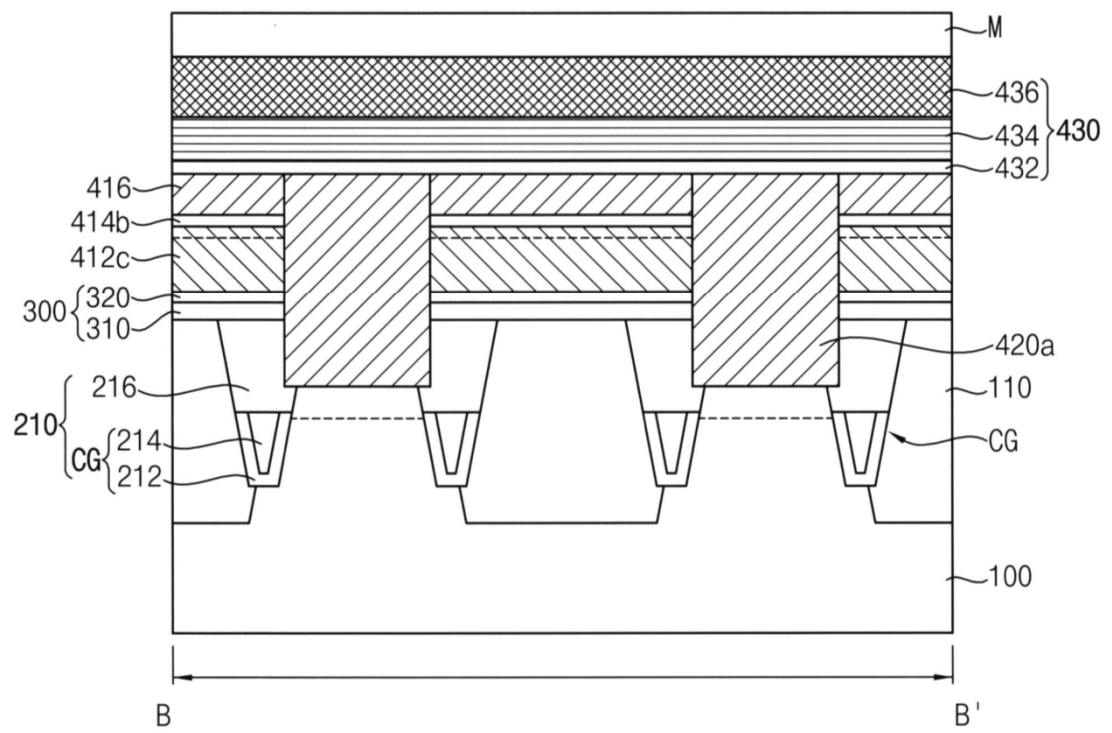


FIG. 18C

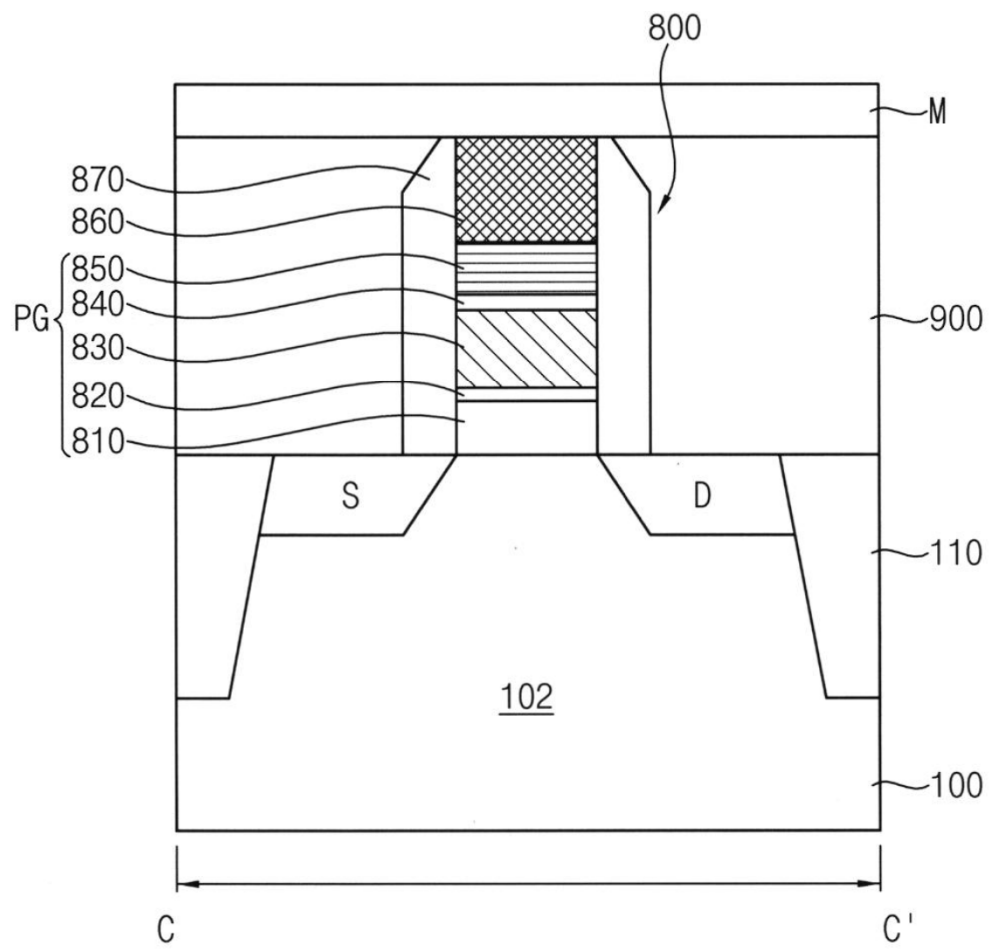


FIG. 18D

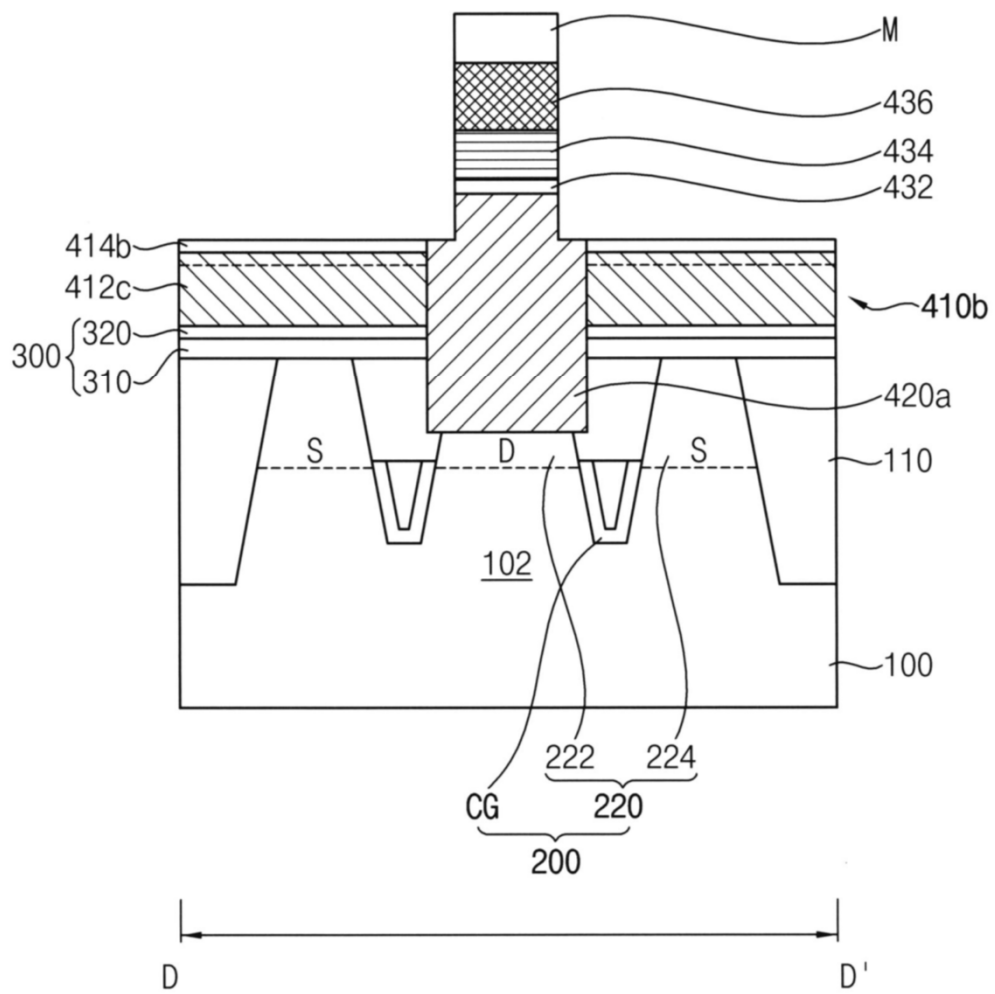


FIG. 19A

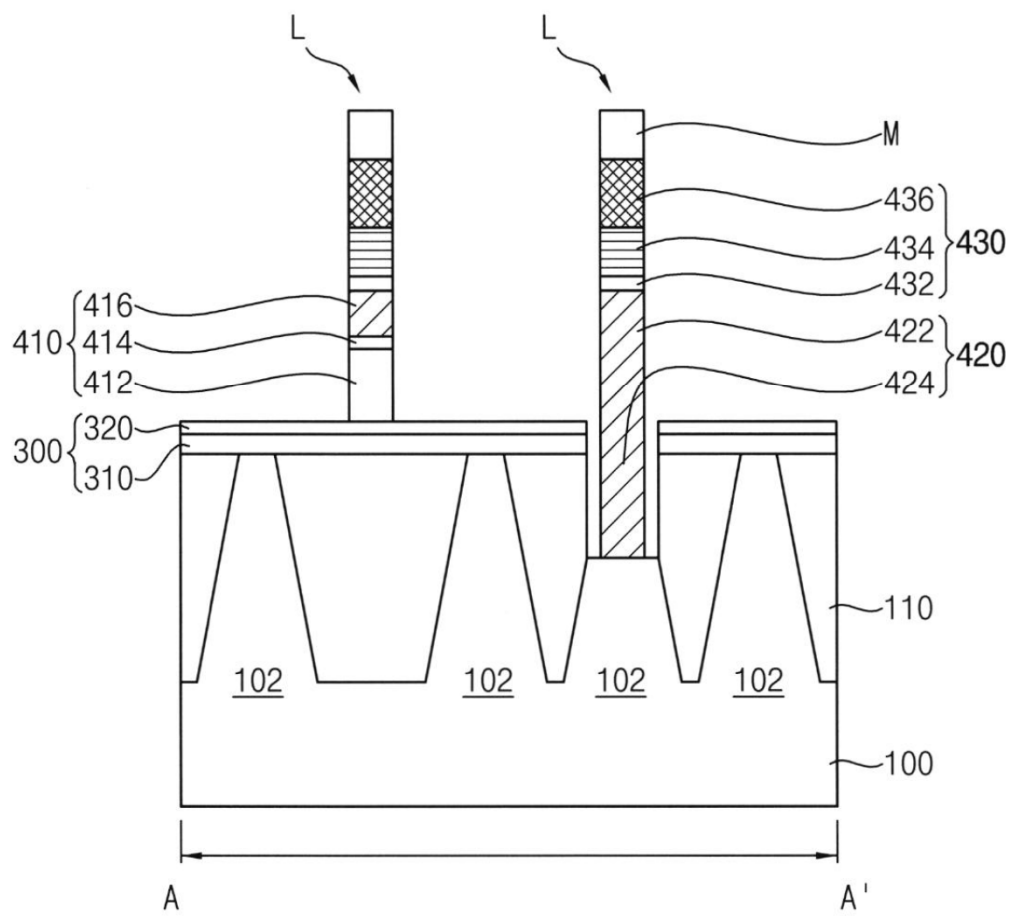


FIG. 19B

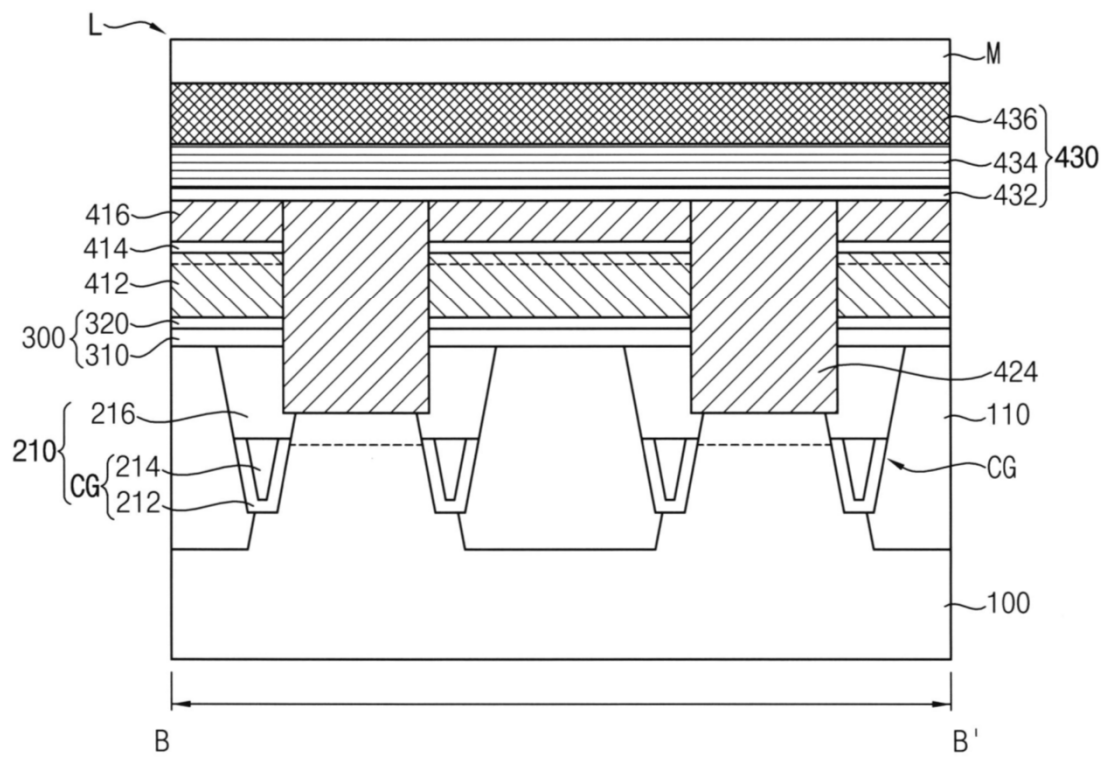


FIG. 19C

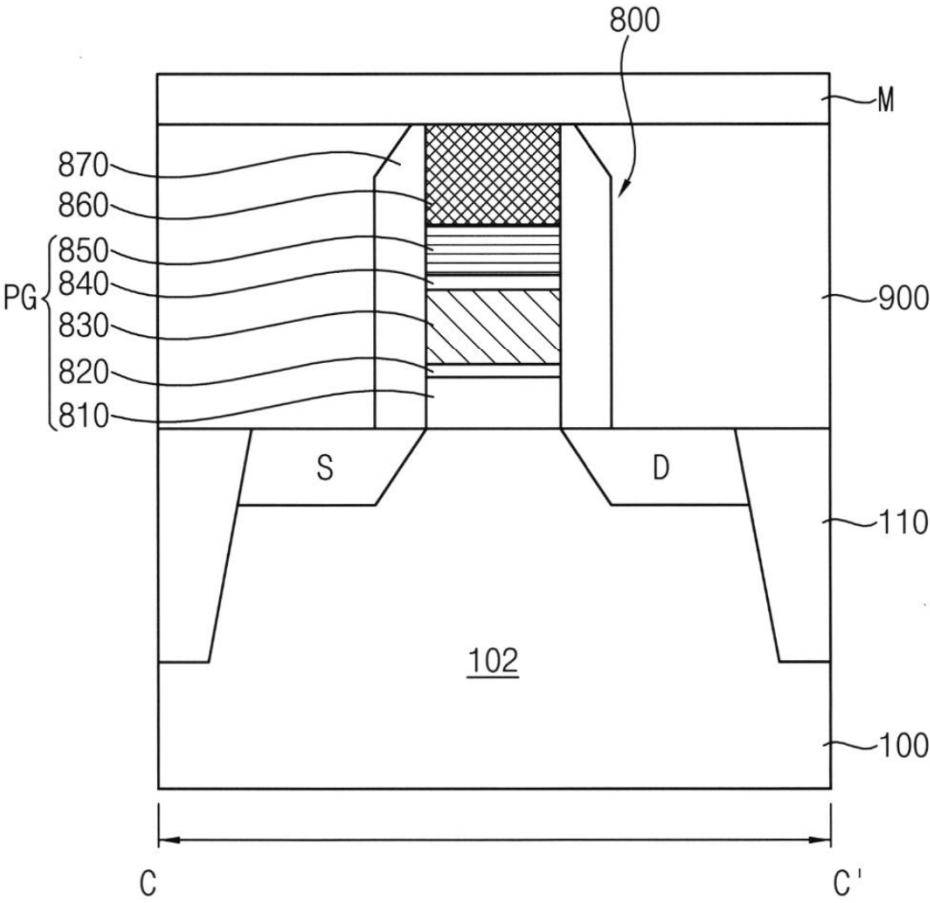


FIG. 19D

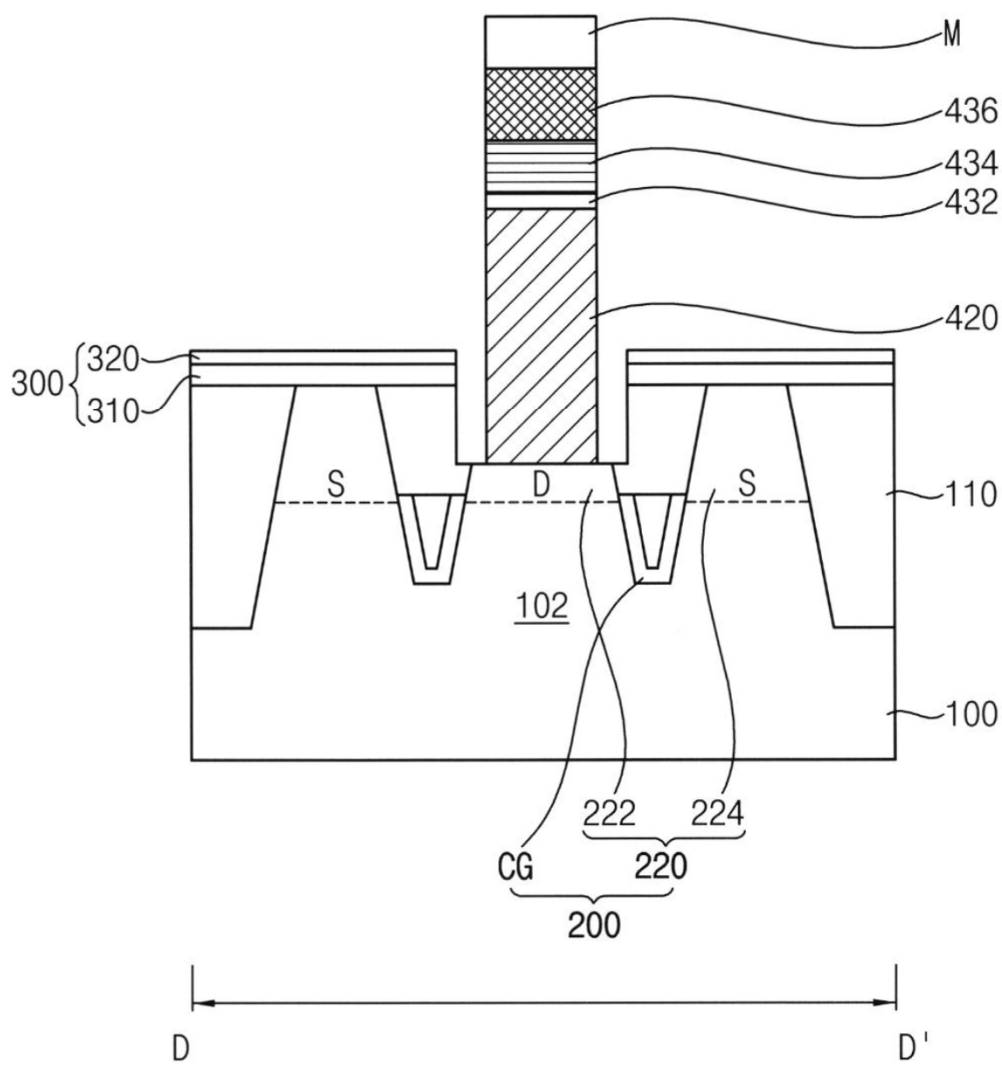


FIG. 20A

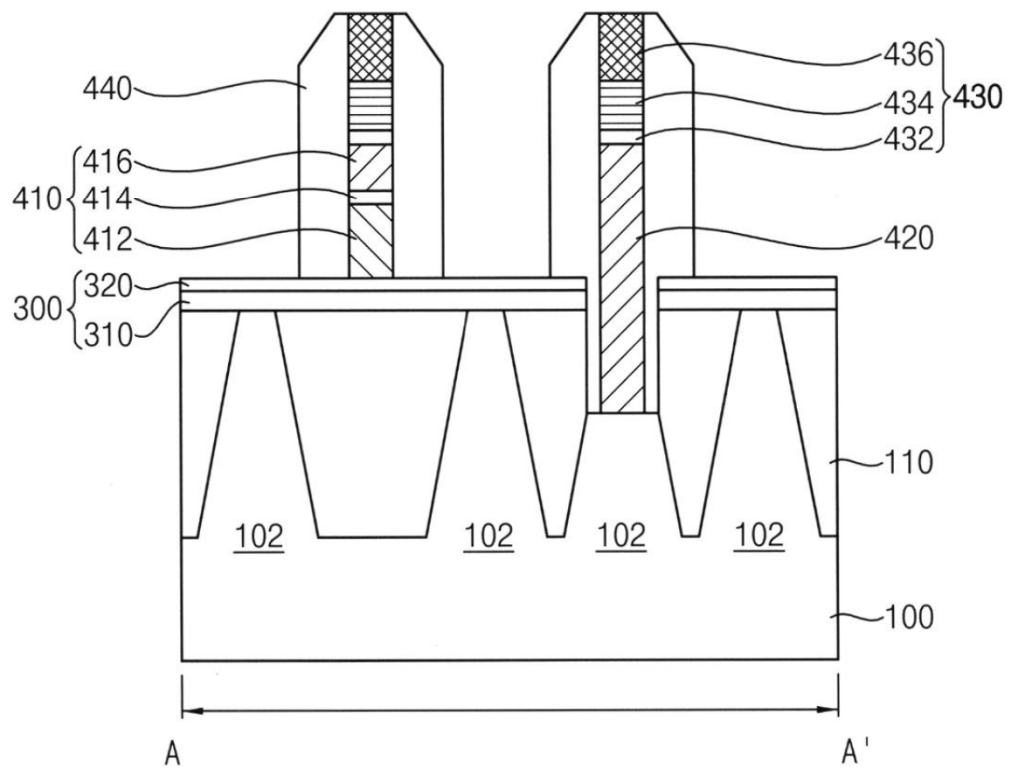


FIG. 20B

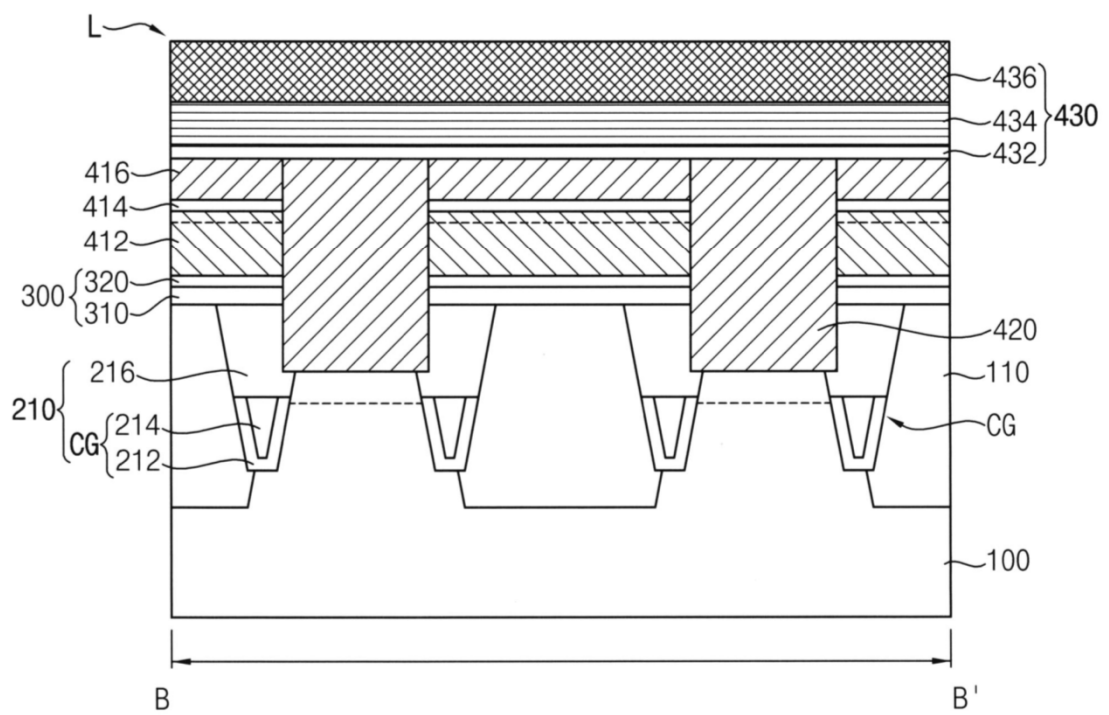


FIG. 20C

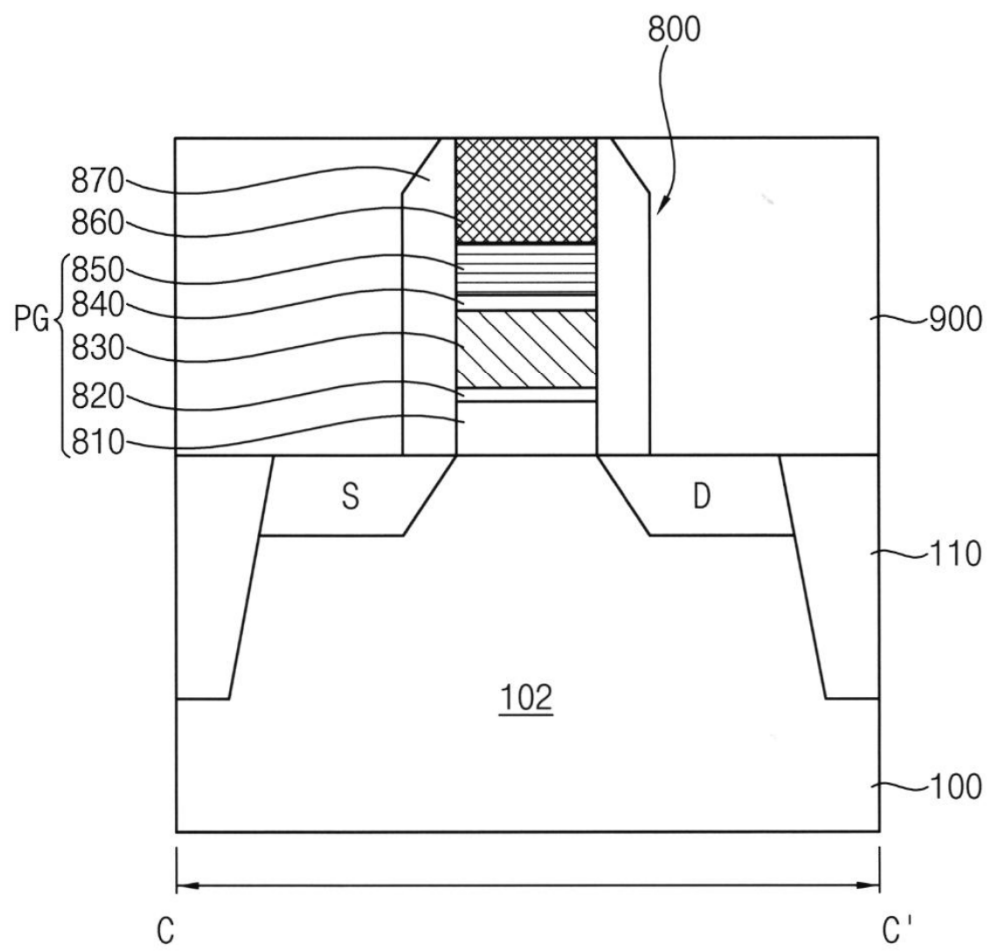


FIG. 20D

